

LME49870

44V Single High Performance, High Fidelity Audio Operational Amplifier

General Description

The LME49870 is part of the ultra-low distortion, low noise, high slew rate operational amplifier series optimized and fully specified for high performance, high fidelity applications. Combining advanced leading-edge process technology with state-of-the-art circuit design, the LME49870 audio operational amplifier delivers superior audio signal amplification for outstanding audio performance. The LME49870 combines extremely low voltage noise density ($2.7\text{nV}/\sqrt{\text{Hz}}$) with vanishingly low THD+N (0.00003%) to easily satisfy the most demanding audio applications. To ensure that the most challenging loads are driven without compromise, the LME49870 has a high slew rate of $\pm 20\text{V}/\mu\text{s}$ and an output current capability of $\pm 26\text{mA}$. Further, dynamic range is maximized by an output stage that drives $2\text{k}\Omega$ loads to within 1V of either power supply voltage and to within 1.4V when driving 600Ω loads.

The LME49870's outstanding CMRR (120dB), PSRR (120dB), and V_{OS} (0.1mV) give the amplifier excellent operational amplifier DC performance.

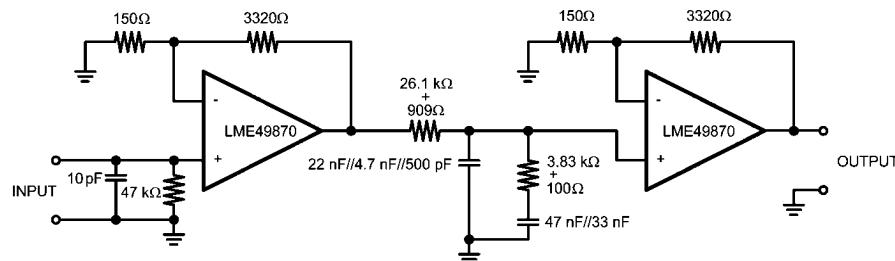
The LME49870 has a wide supply range of $\pm 2.5\text{V}$ to $\pm 22\text{V}$. Over this supply range the LME49870 maintains excellent common-mode rejection, power supply rejection, and low input bias current. The LME49870 is unity gain stable. This Audio Operational Amplifier achieves outstanding AC performance while driving complex loads with values as high as 100pF.

The LME49870 is available in 8-lead narrow body SOIC. Demonstration boards are available for each package.

Key Specifications

- Power Supply Voltage Range $\pm 2.5\text{V}$ to $\pm 22\text{V}$
- THD+N
 $(A_V = 1, V_{OUT} = 3V_{RMS}, f_{IN} = 1\text{kHz})$

Typical Application



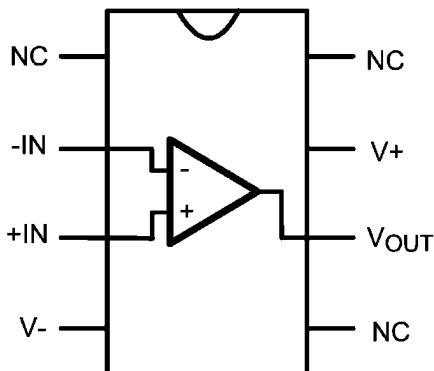
Note: 1% metal film resistors, 5% polypropylene capacitors

Passively Equalized RIAA Phono Preamplifier

300194k5

Connection Diagrams

www.DataSheet4U.com



30019401

Order Number LME49870MA
See NS Package Number — M08A

LME49870 Top Mark



30019402

N — National Logo
Z — Assembly Plant code
X — 1 Digit Date code
TT — Die Traceability
L49870 — LME49870
MA — Package code

Absolute Maximum Ratings (Notes 1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Power Supply Voltage ($V_S = V^+ - V^-$)	46V
Storage Temperature	-65°C to 150°C
Input Voltage	(V-) - 0.7V to (V+) + 0.7V
Output Short Circuit (Note 3)	Continuous
Power Dissipation	Internally Limited
ESD Rating (Note 4)	2000V
ESD Rating (Note 5)	

Pins 1, 4, 7 and 8	200V
Pins 2, 3, 5 and 6	100V
Junction Temperature	150°C
Thermal Resistance	
θ_{JA} (SO)	145°C/W

Operating Ratings

Temperature Range	
$T_{MIN} \leq T_A \leq T_{MAX}$	-40°C ≤ T_A ≤ 85°C
Supply Voltage Range	$\pm 2.5V \leq V_S \leq \pm 22V$

Electrical Characteristics for the LME49870 (Note 1) The following specifications apply for $V_S = \pm 18V$ and $\pm 22V$, $R_L = 2k\Omega$, $R_{SOURCE} = 10\Omega$, $f_{IN} = 1kHz$, $T_A = 25^\circ C$, unless otherwise specified.

Symbol	Parameter	Conditions	LME49870		Units (Limits)
			Typical	Limit	
			(Note 6)	(Note 7)	
THD+N	Total Harmonic Distortion + Noise	$A_V = 1$, $V_{OUT} = 3V_{rms}$ $R_L = 2k\Omega$ $R_L = 600\Omega$	0.00003	0.00009	% (max)
IMD	Intermodulation Distortion	$A_V = 1$, $V_{OUT} = 3V_{RMS}$ Two-tone, 60Hz & 7kHz 4:1	0.00005		%
GBWP	Gain Bandwidth Product		55	45	MHz (min)
SR	Slew Rate		± 20	± 15	V/ μ s (min)
FPBW	Full Power Bandwidth	$V_{OUT} = 1V_{P-P}$, -3dB referenced to output magnitude at $f = 1kHz$	10		MHz
t_s	Settling time	$A_V = -1$, 10V step, $C_L = 100pF$ 0.1% error range	1.2		μ s
e_n	Equivalent Input Noise Voltage	$f_{BW} = 20Hz$ to $20kHz$	0.34	0.65	μV_{RMS} (max)
	Equivalent Input Noise Density	$f = 1kHz$ $f = 10Hz$	2.5 6.4	4.7	nV/ \sqrt{Hz} (max)
i_n	Current Noise Density	$f = 1kHz$ $f = 10Hz$	1.6 3.1		pA/ \sqrt{Hz}
V_{OS}	Offset Voltage	$V_S = \pm 18V$	± 0.12		mV (max)
		$V_S = \pm 22V$	± 0.14	± 0.7	mV (max)
$\Delta V_{OS}/\Delta Temp$	Average Input Offset Voltage Drift vs Temperature	$-40^\circ C \leq T_A \leq 85^\circ C$	0.1		$\mu V/^\circ C$
PSRR	Average Input Offset Voltage Shift vs Power Supply Voltage	$V_S = \pm 18V$, $\Delta V_S = 24V$ (Note 8) $V_S = \pm 22V$, $\Delta V_S = 30V$	120 120	110	dB (min)
I_B	Input Bias Current	$V_{CM} = 0V$	10	72	nA (max)
$\Delta I_{OS}/\Delta Temp$	Input Bias Current Drift vs Temperature	$-40^\circ C \leq T_A \leq 85^\circ C$	0.2		nA/ $^\circ C$
I_{OS}	Input Offset Current	$V_{CM} = 0V$	11	65	nA (max)
V_{IN-CM}	Common-Mode Input Voltage Range	$V_S = \pm 18V$	+17.1 -16.9		V (min) V (min)
		$V_S = \pm 22V$	+21.0 -20.8	(V+) - 2.0 (V-) + 2.0	V (min) V (min)

Symbol	Parameter	Conditions	LME49870		Units (Limits)
			Typical	Limit	
			(Note 6)	(Note 7)	
CMRR	Common-Mode Rejection	$V_S = \pm 18V$ $-12V \leq V_{cm} \leq 12V$	120		dB (min)
		$V_S = \pm 22V$ $-15V \leq V_{cm} \leq 15V$	120	110	
Z_{IN}	Differential Input Impedance		30		kΩ
	Common Mode Input Impedance	$-10V < V_{cm} < 10V$	1000		MΩ
A_{VOL}	Open Loop Voltage Gain	$V_S = \pm 18V$ $-12V \leq V_{out} \leq 12V$ $R_L = 600\Omega$ $R_L = 2k\Omega$ $R_L = 10\Omega$	140		dB
		$V_S = \pm 22V$ $-15V \leq V_{out} \leq 15V$ $R_L = 600\Omega$ $R_L = 2k\Omega$ $R_L = 10\Omega$	140	125	
		$R_L = 600\Omega$ $V_S = \pm 18V$ $V_S = \pm 22V$	140		
		$R_L = 2k\Omega$ $V_S = \pm 18V$ $V_S = \pm 22V$	140		
		$R_L = 10k\Omega$ $V_S = \pm 18V$ $V_S = \pm 22V$	140		dB
		$R_L = 600\Omega$ $V_S = \pm 20V$ $V_S = \pm 22V$	140		
		$R_L = 2k\Omega$ $V_S = \pm 20V$ $V_S = \pm 22V$	140		
		$R_L = 10k\Omega$ $V_S = \pm 20V$ $V_S = \pm 22V$	140		
V_{OUTMAX}	Maximum Output Voltage Swing	$R_L = 600\Omega$ $V_S = \pm 18V$ $V_S = \pm 22V$	±16.7		V (min)
		$R_L = 2k\Omega$ $V_S = \pm 18V$ $V_S = \pm 22V$	±20.4	±19.0	
		$R_L = 10k\Omega$ $V_S = \pm 18V$ $V_S = \pm 22V$	±17.0		V (min)
I_{OUT}	Output Current	$R_L = 600\Omega$ $V_S = \pm 20V$ $V_S = \pm 22V$	±17.1		V (min)
		$R_L = 2k\Omega$ $V_S = \pm 20V$ $V_S = \pm 22V$	±21.0		
		$R_L = 10k\Omega$ $V_S = \pm 20V$ $V_S = \pm 22V$	±21.0		V (min)
I_{OUT-CC}	Instantaneous Short Circuit Current	$R_L = 600\Omega$ $V_S = \pm 20V$ $V_S = \pm 22V$	±31		mA (min)
		$R_L = 2k\Omega$ $V_S = \pm 20V$ $V_S = \pm 22V$	±37	±30	
R_{OUT}	Output Impedance	$f_{IN} = 10kHz$ Closed-Loop Open-Loop	0.01		Ω
			13		
C_{LOAD}	Capacitive Load Drive Overshoot	100pF	16		%
I_S	Total Quiescent Current	$I_{OUT} = 0mA$	5	6.5	mA (max)

Note 1: “Absolute Maximum Ratings” indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the *Absolute Maximum Ratings* or other conditions beyond those indicated in the *Recommended Operating Conditions* is not implied. The *Recommended Operating Conditions* indicate conditions at which the device is functional and the device should not be operated beyond such conditions. All voltages are measured with respect to the ground pin, unless otherwise specified.

Note 2: The *Electrical Characteristics* tables list guaranteed specifications under the listed *Recommended Operating Conditions* except as otherwise modified or specified by the *Electrical Characteristics Conditions* and/or Notes. Typical specifications are estimations only and are not guaranteed.

Note 3: The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{JMAX} , θ_{JA} , and the ambient temperature, T_A . The maximum allowable power dissipation is $P_{DMAX} = (T_{JMAX} - T_A) / \theta_{JA}$ or the number given in *Absolute Maximum Ratings*, whichever is lower.

Note 4: Human body model, applicable std. JESD22-A114C.

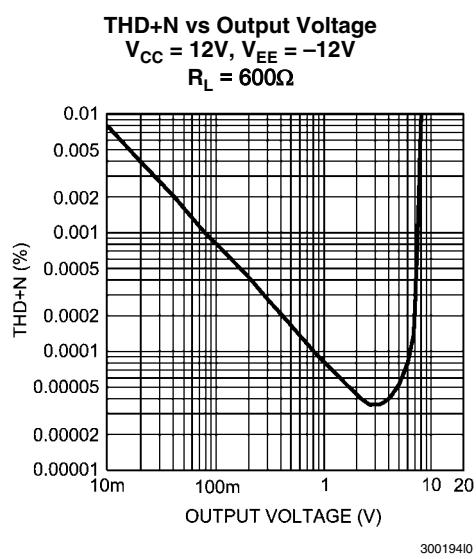
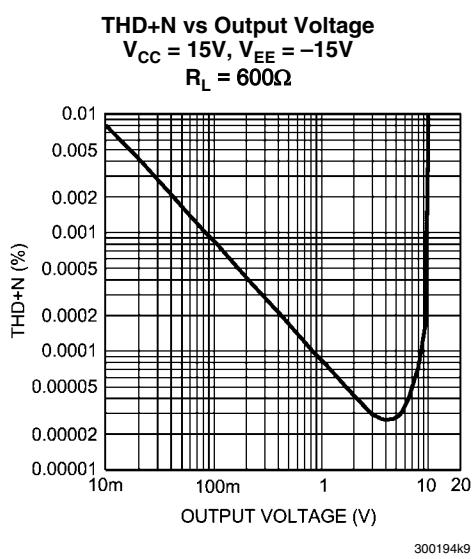
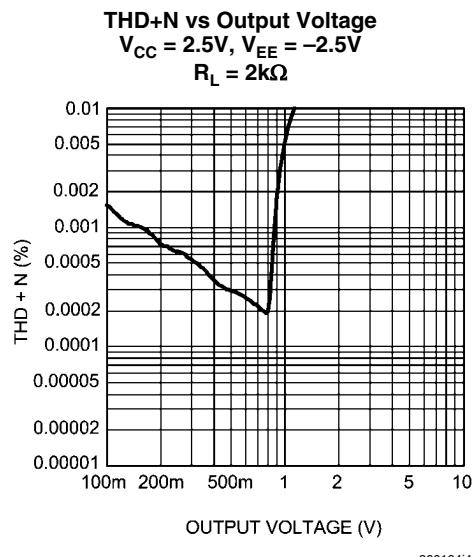
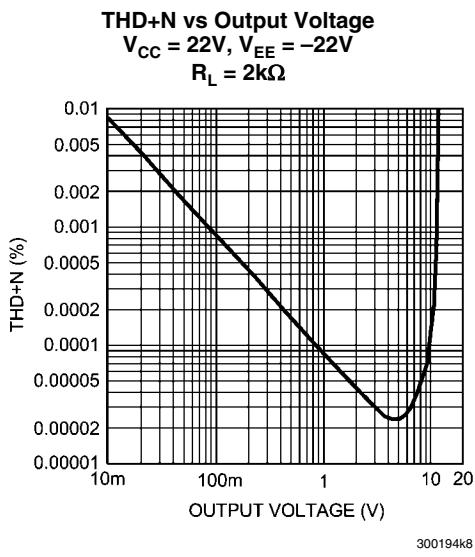
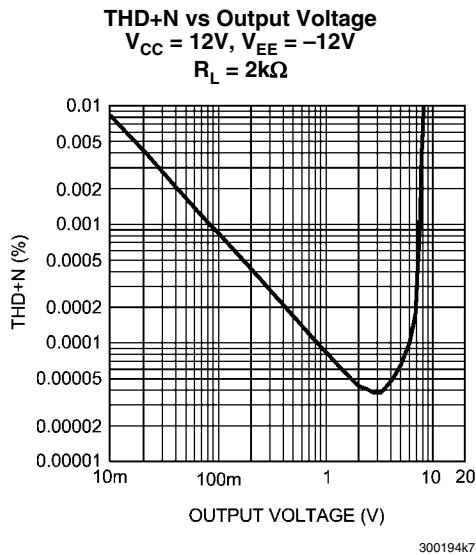
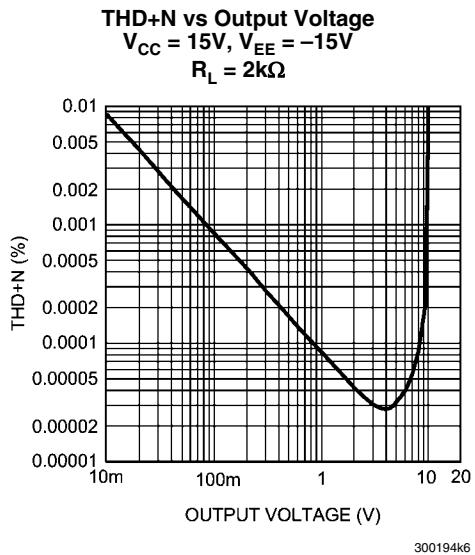
Note 5: Machine model, applicable std. JESD22-A115-A.

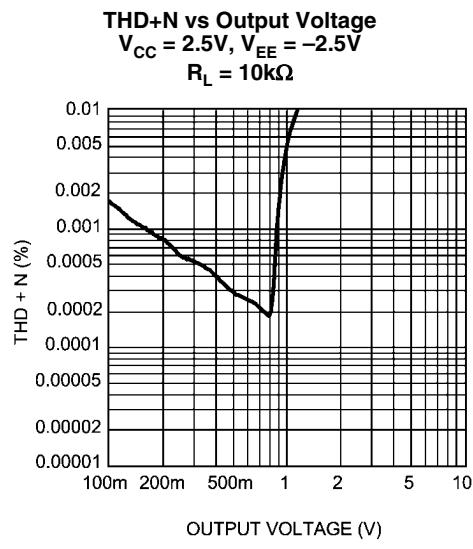
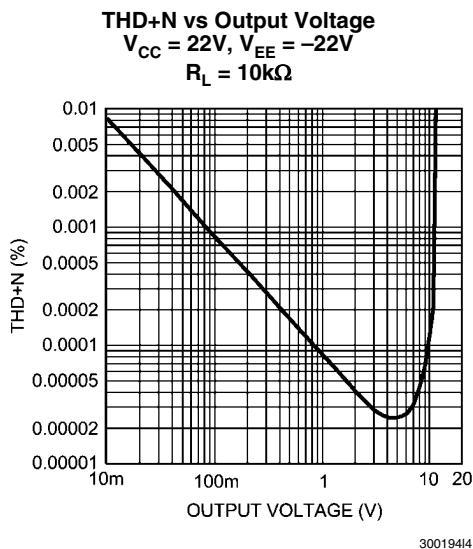
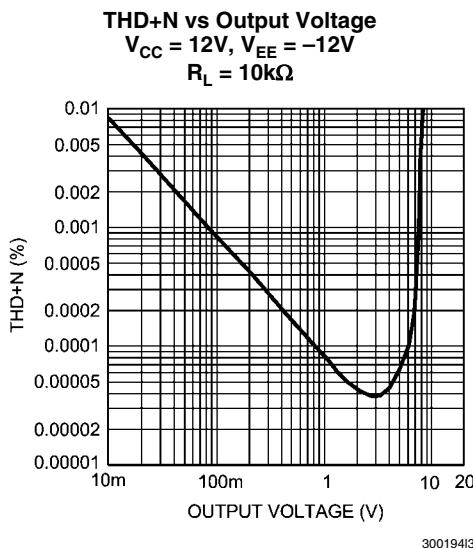
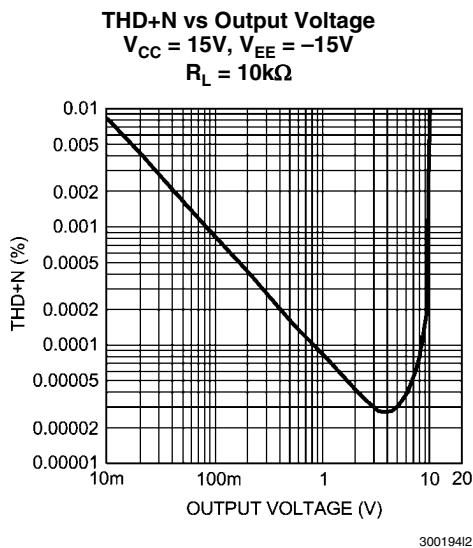
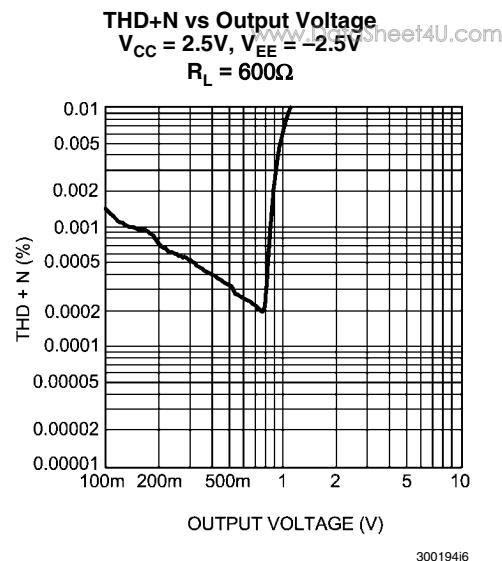
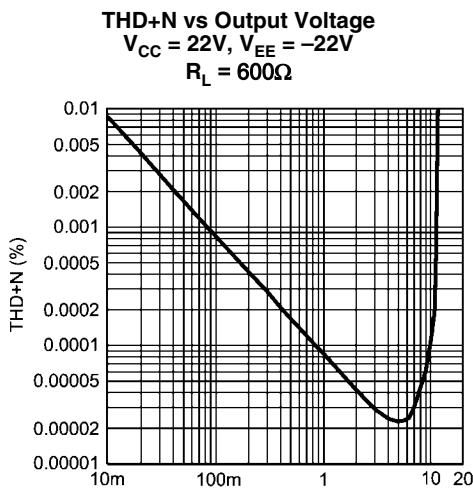
Note 6: Typical values represent most likely parametric norms at $T_A = +25^\circ C$, and at the *Recommended Operation Conditions* at the time of product characterization and are not guaranteed.

Note 7: Datasheet min/max specification limits are guaranteed by test or statistical analysis.

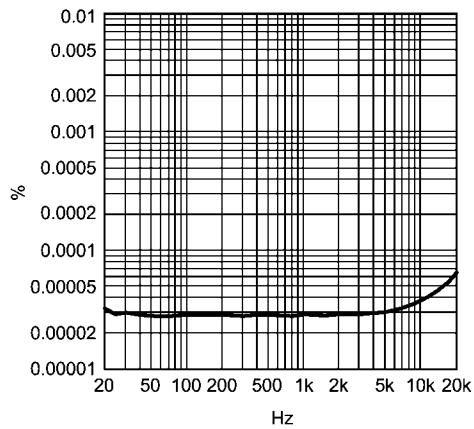
Note 8: PSRR is measured as follows: For V_S , V_{OS} is measured at two supply voltages, ±7V and ±22V, $PSRR = 20\log(\Delta V_{OS}/\Delta V_S)$.

Typical Performance Characteristics

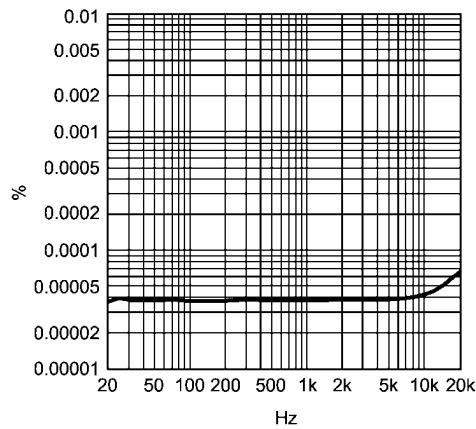




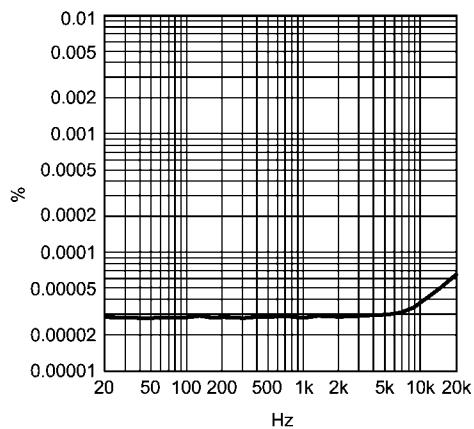
THD+N vs Frequency
 $V_{CC} = 15V$, $V_{EE} = -15V$, $V_{OUT} = 3V_{RMS}$
 $R_L = 2k\Omega$



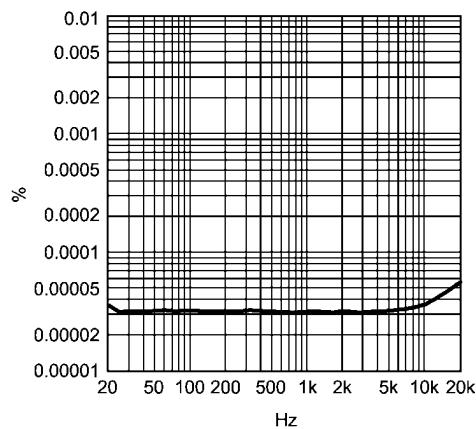
THD+N vs Frequency
 $V_{CC} = 12V$, $V_{EE} = -12V$, $V_{OUT} = 3V_{RMS}$
 $R_L = 2k\Omega$



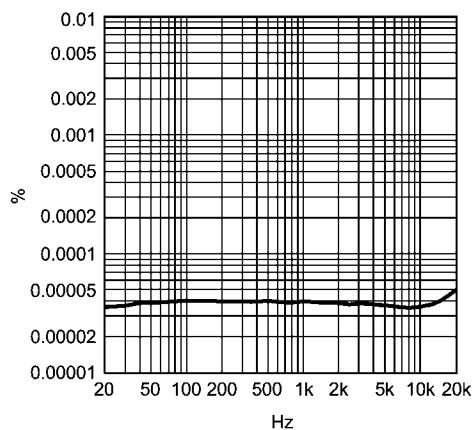
THD+N vs Frequency
 $V_{CC} = 22V$, $V_{EE} = -22V$, $V_{OUT} = 3V_{RMS}$
 $R_L = 2k\Omega$



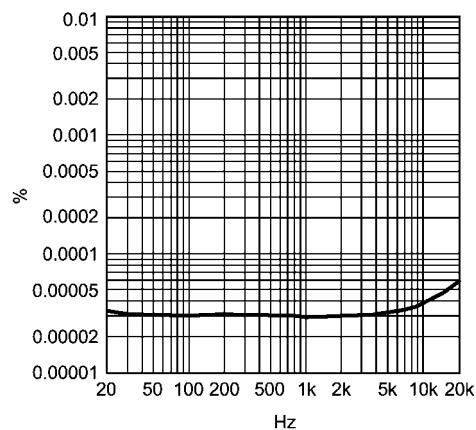
THD+N vs Frequency
 $V_{CC} = 15V$, $V_{EE} = -15V$, $V_{OUT} = 3V_{RMS}$
 $R_L = 600\Omega$

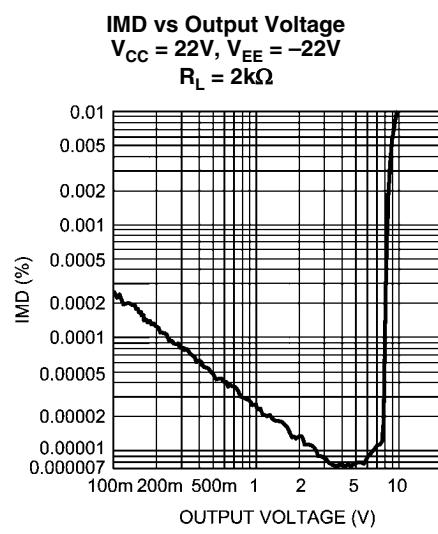
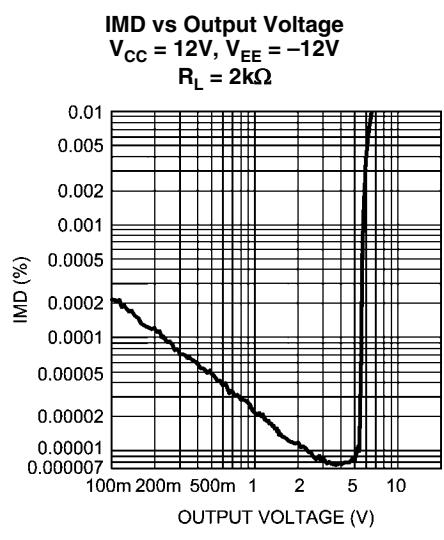
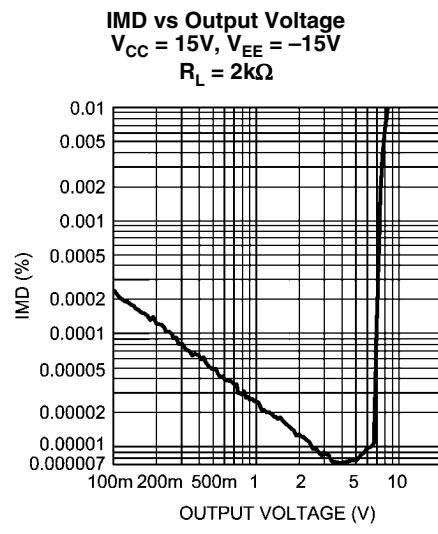
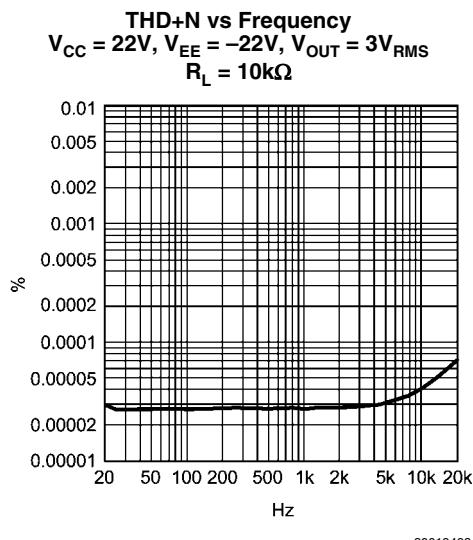
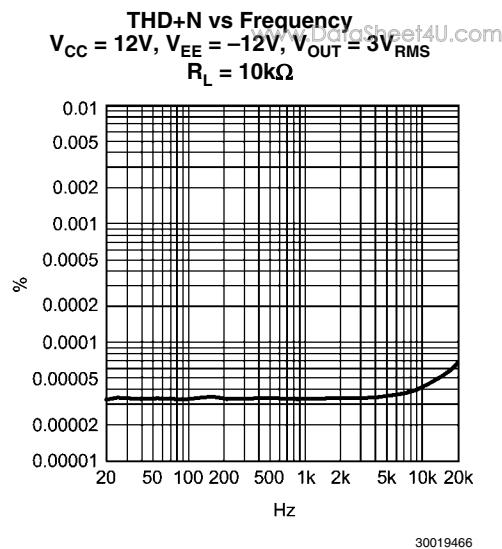
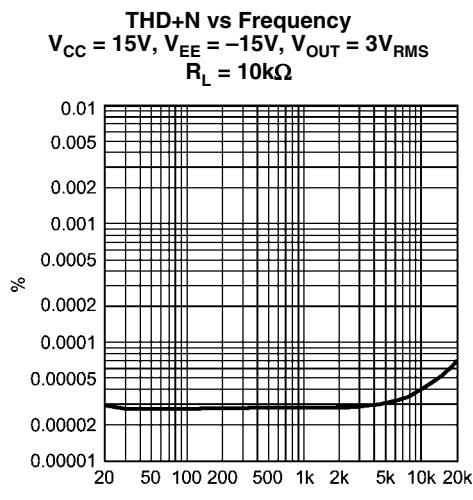


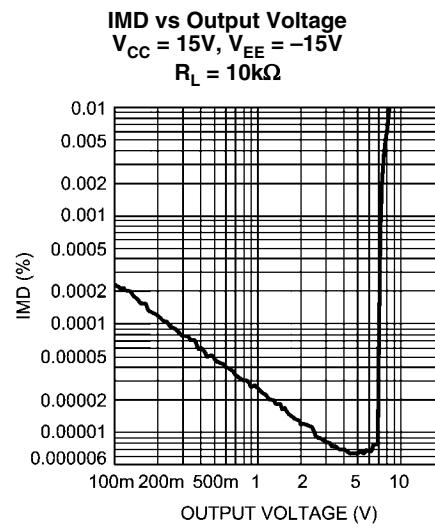
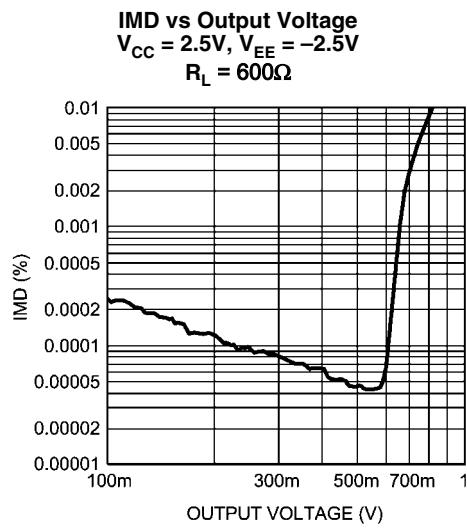
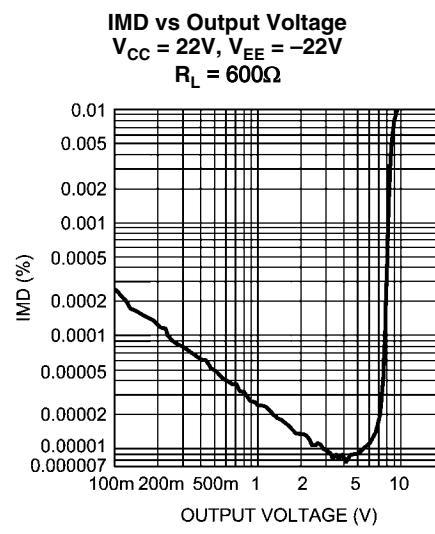
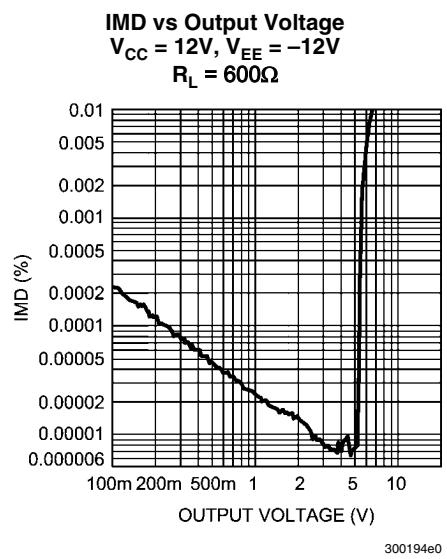
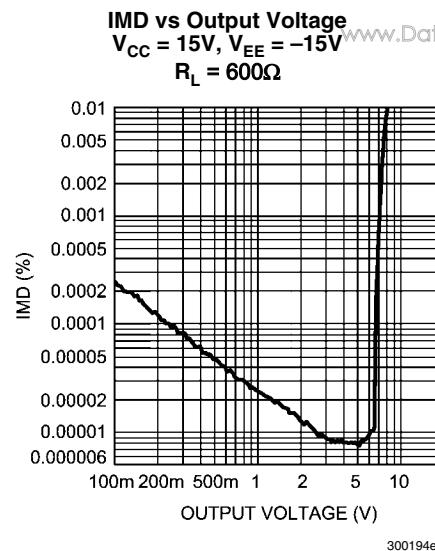
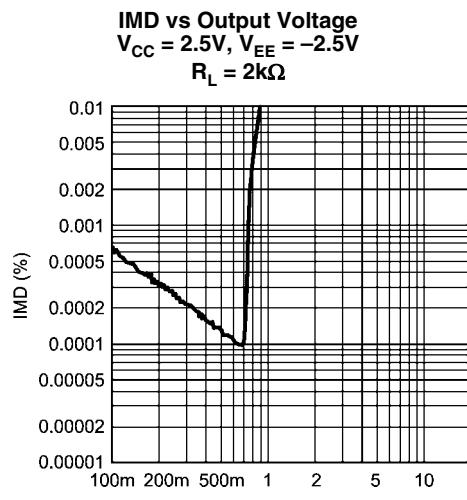
THD+N vs Frequency
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 $R_L = 600\Omega$

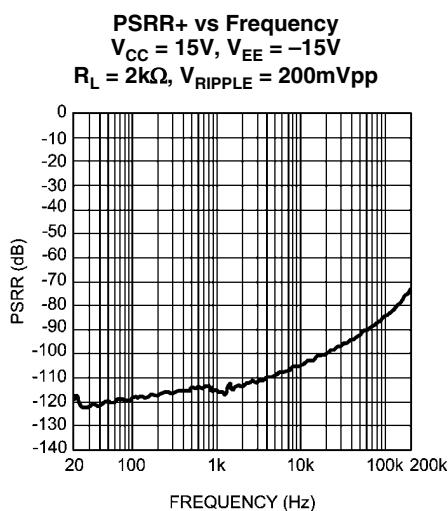
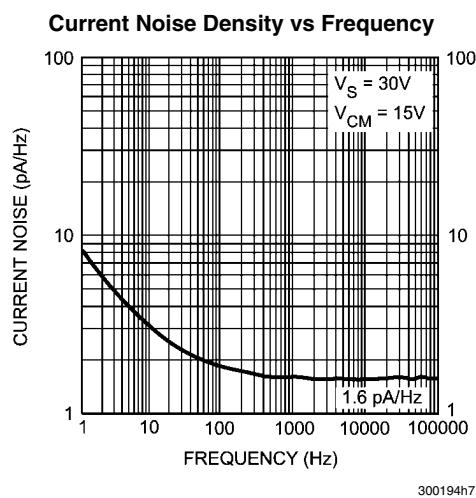
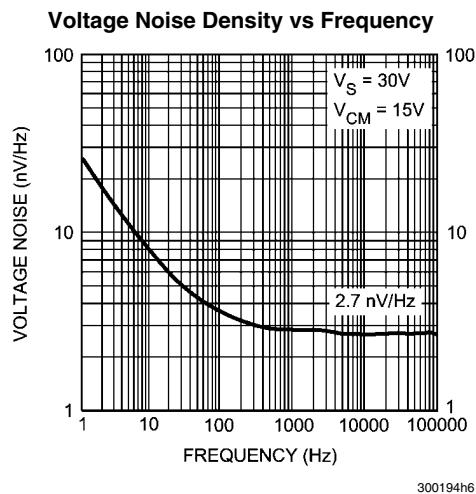
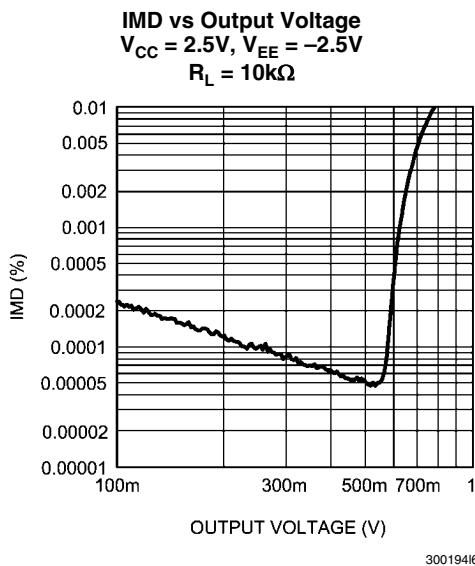
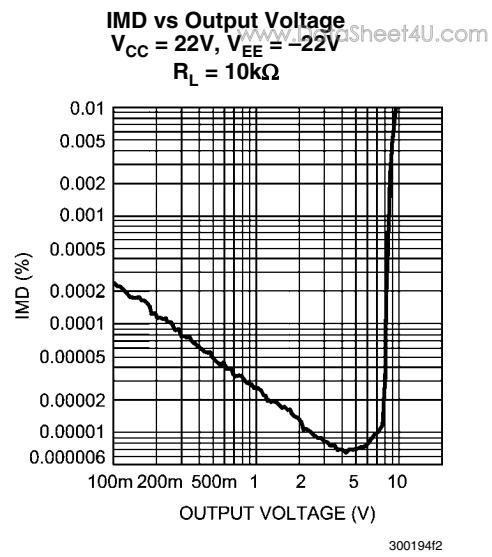
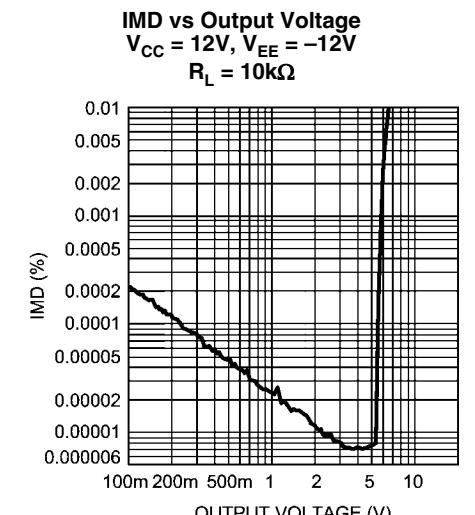


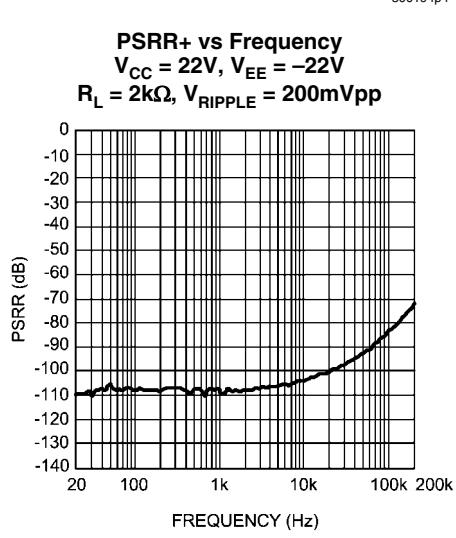
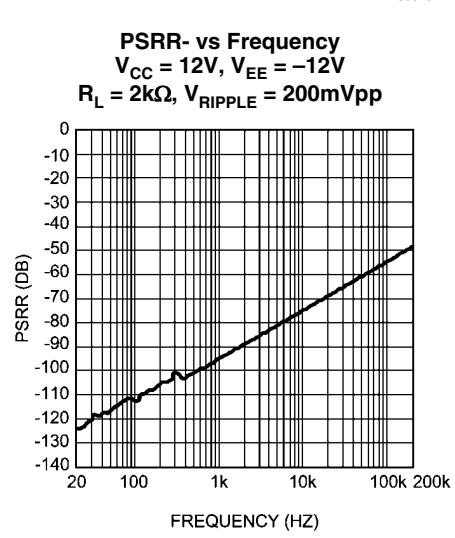
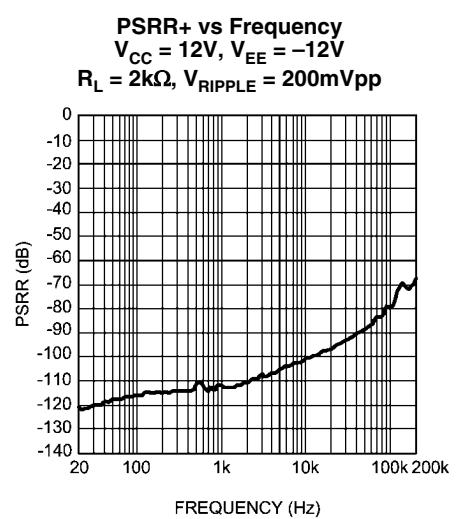
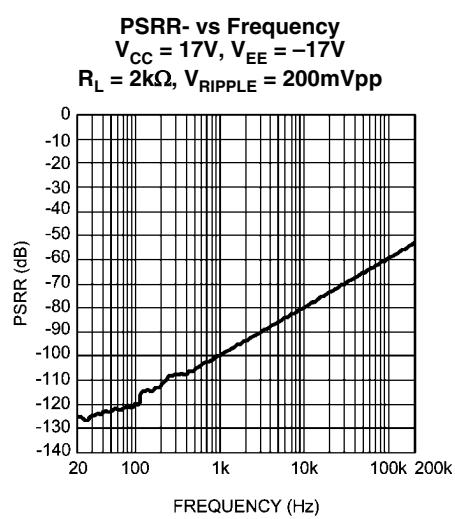
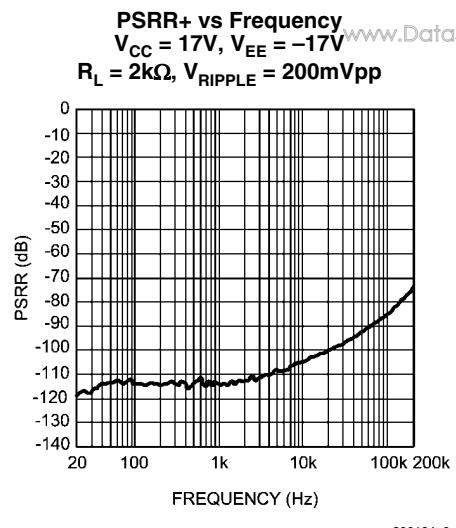
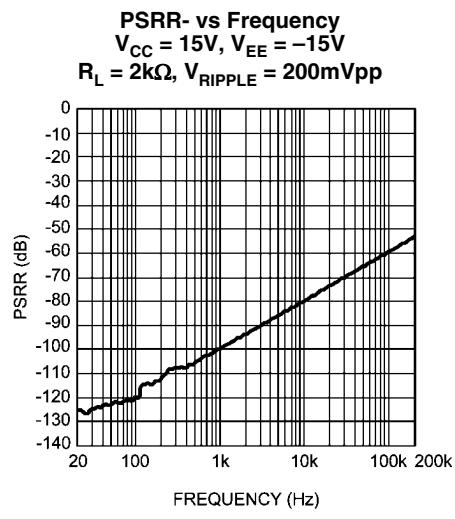
THD+N vs Frequency
 $V_{CC} = 22V$, $V_{EE} = -22V$, $V_{OUT} = 3V_{RMS}$
 $R_L = 600\Omega$

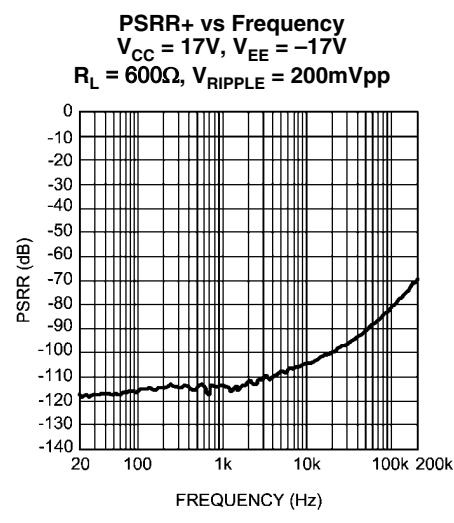
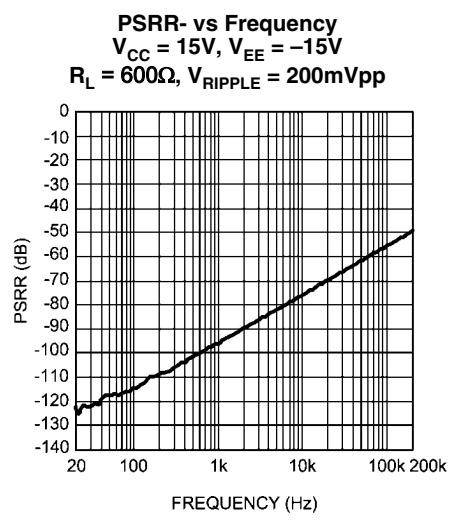
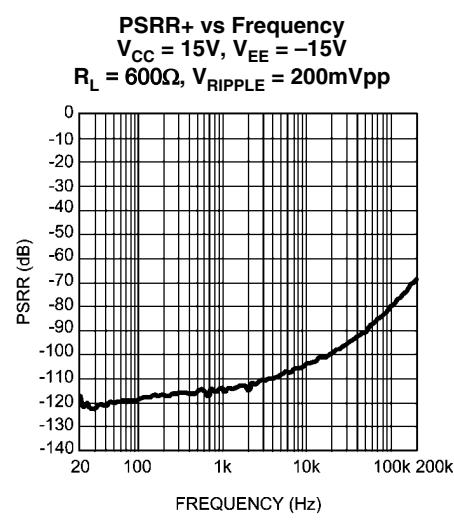
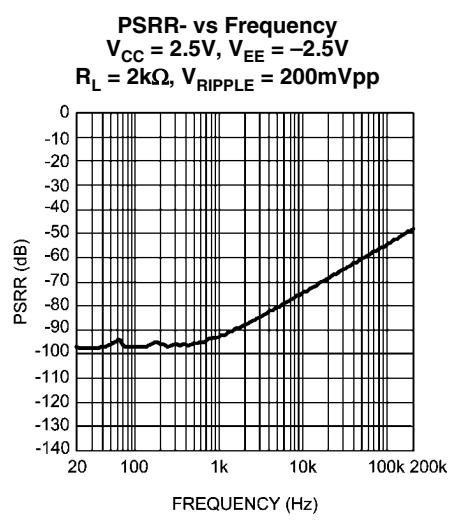
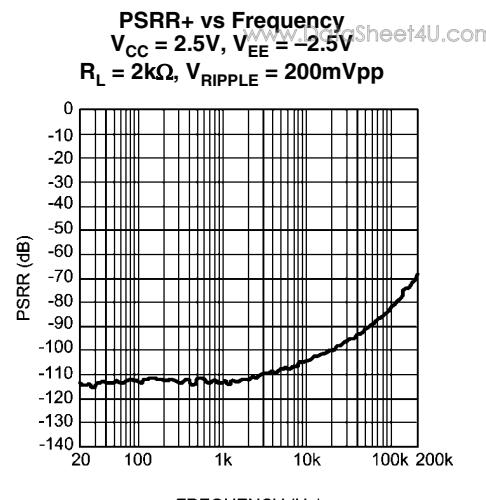
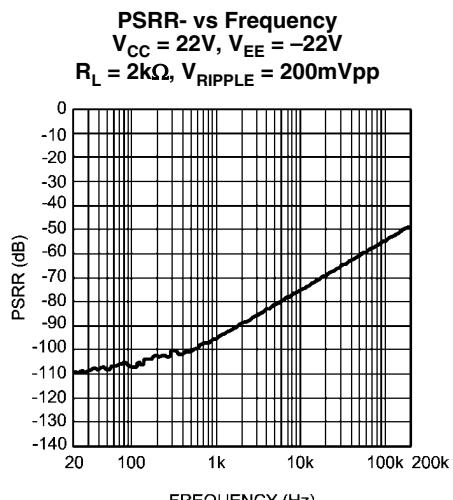


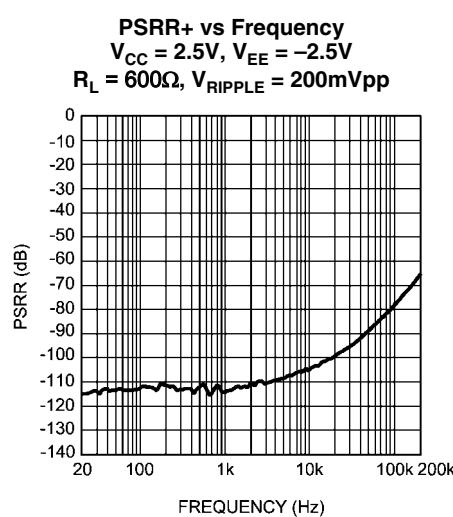
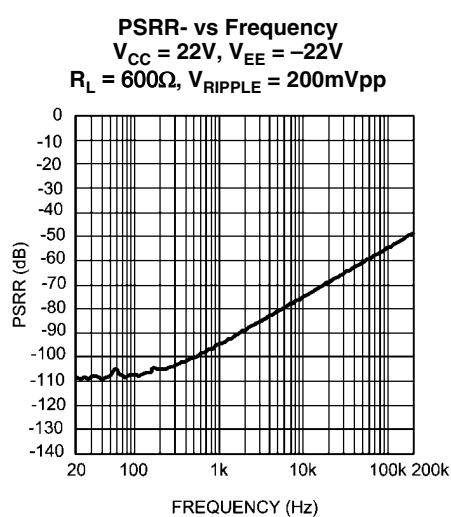
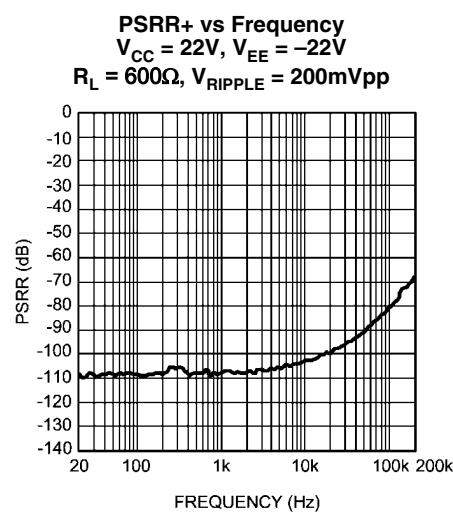
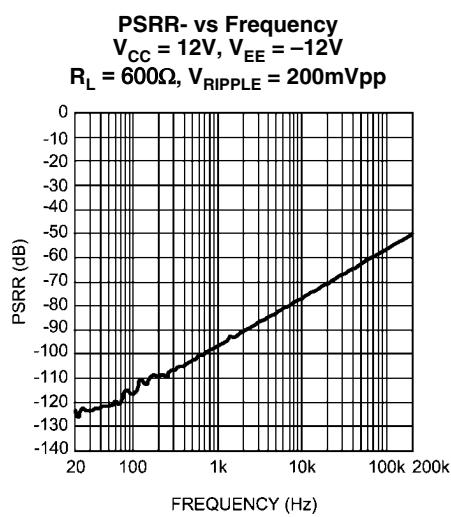
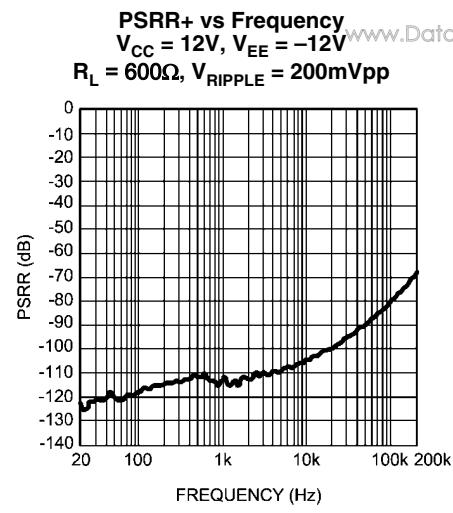
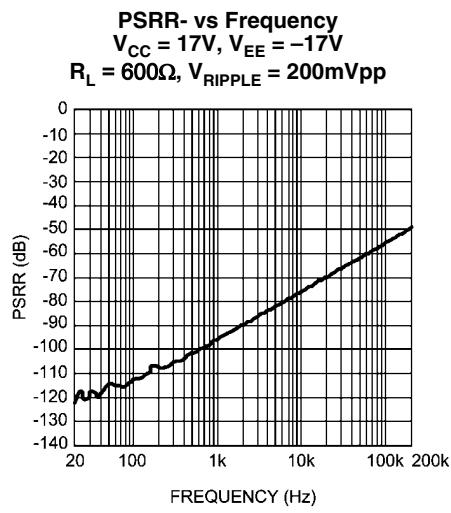


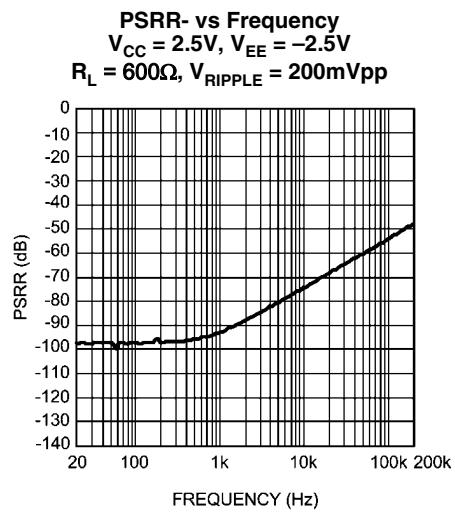




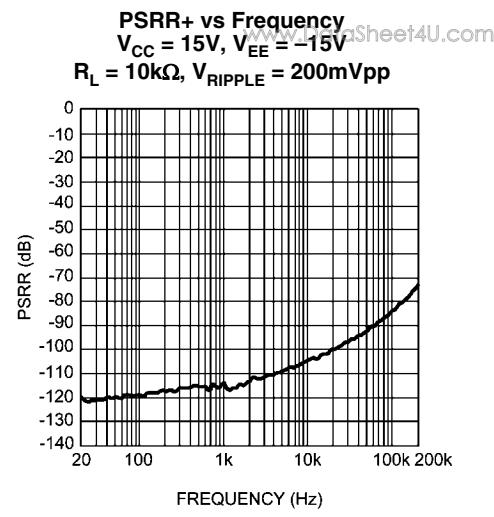




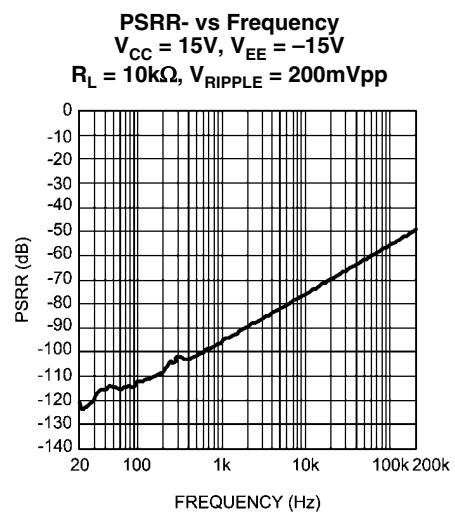




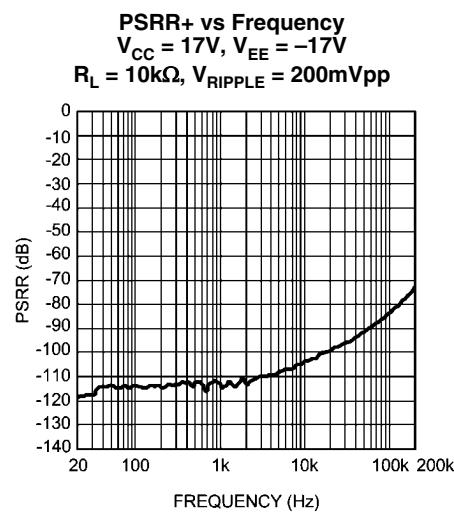
300194q8



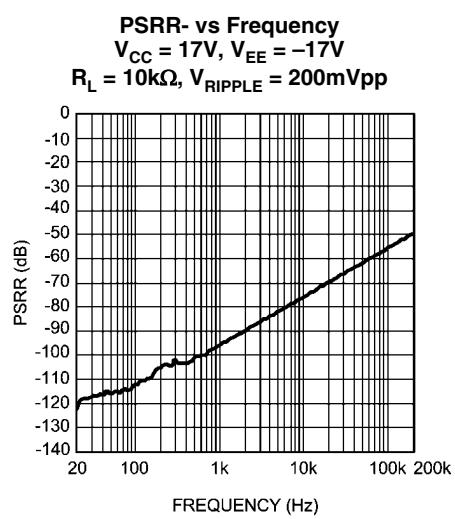
300194p8



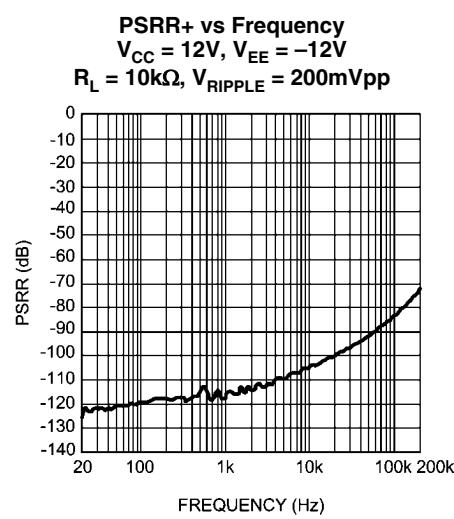
300194r3



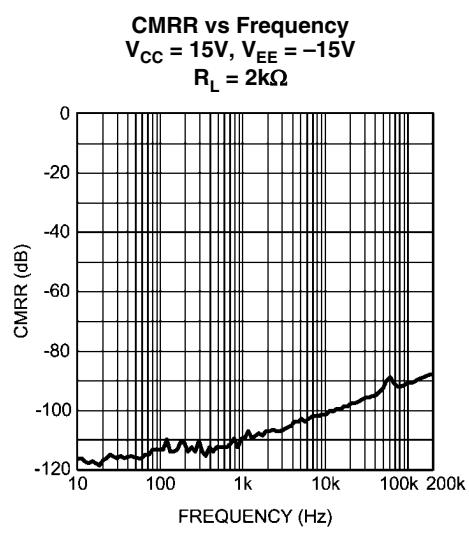
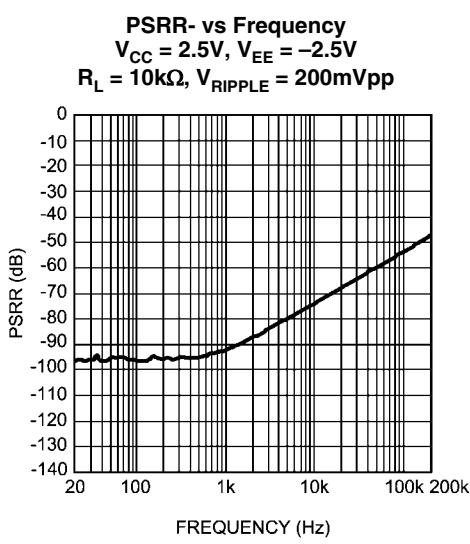
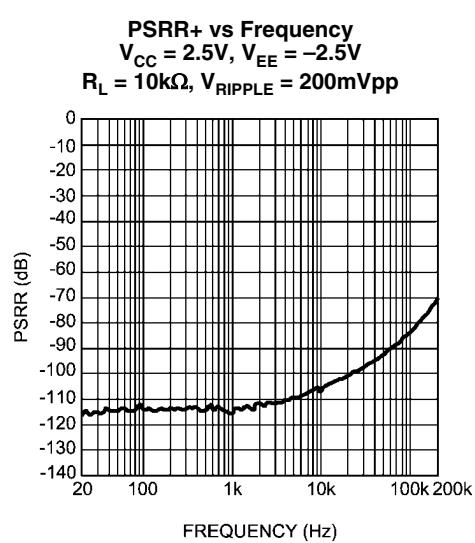
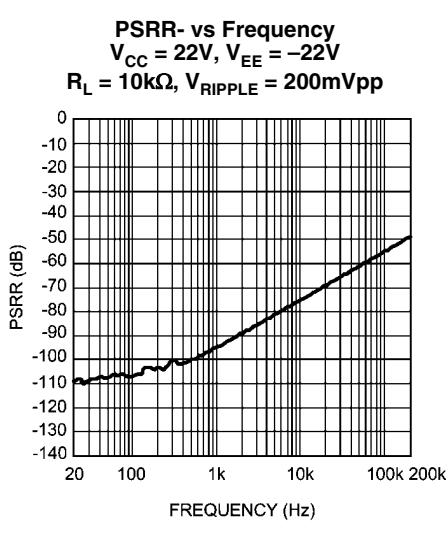
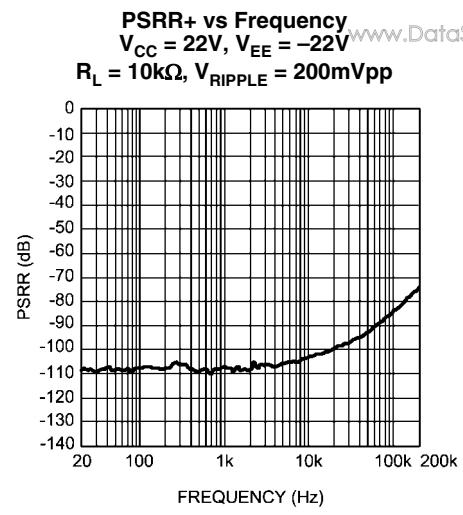
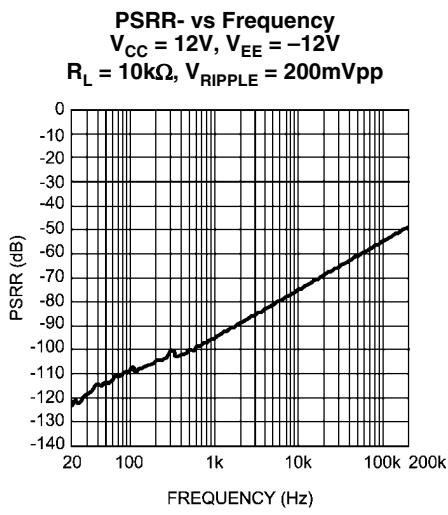
300194q1

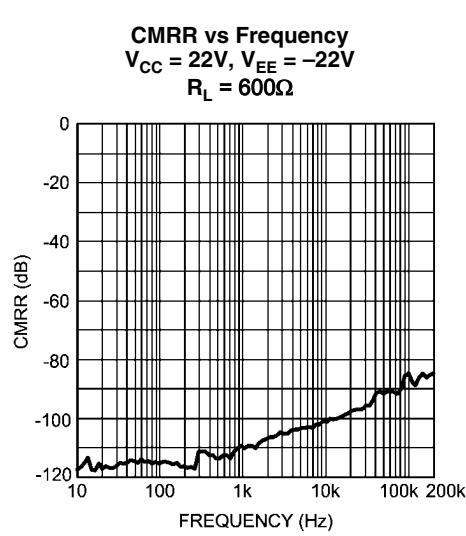
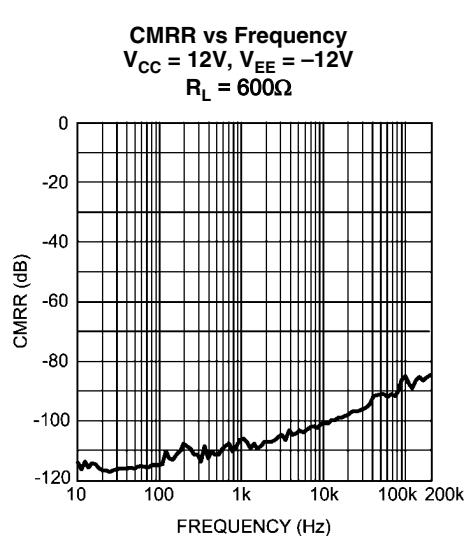
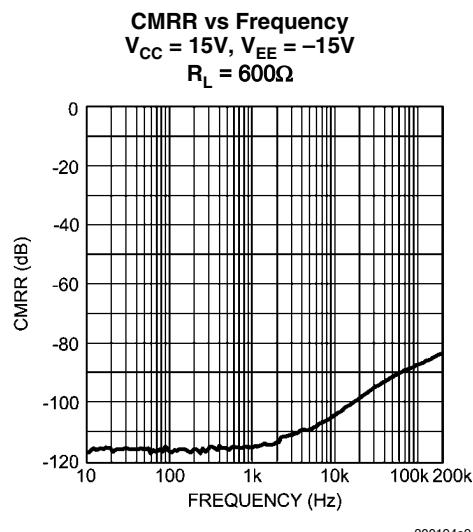
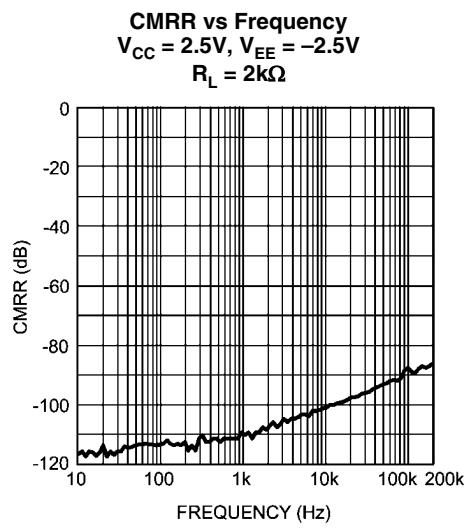
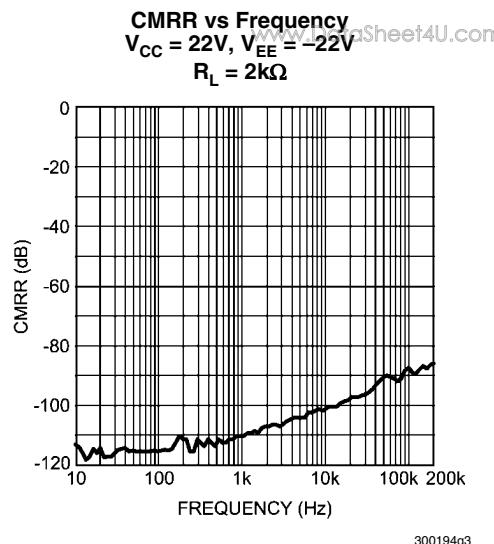
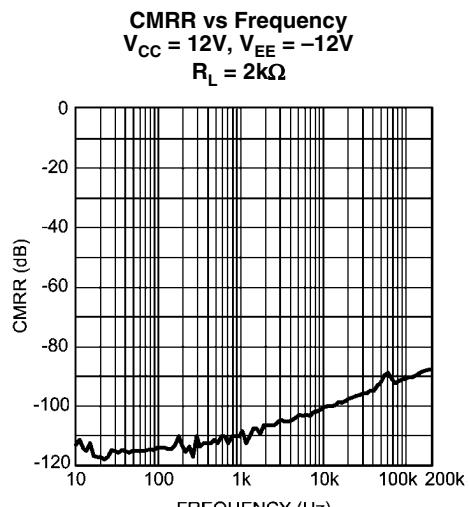


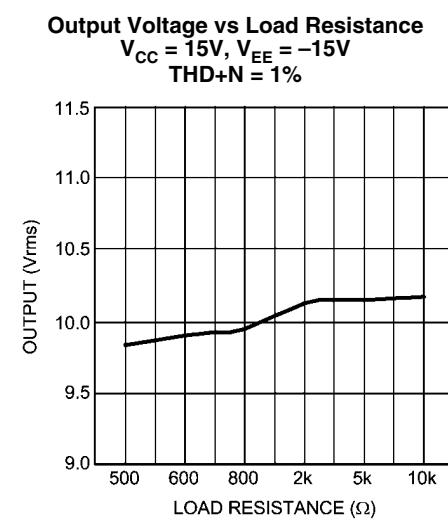
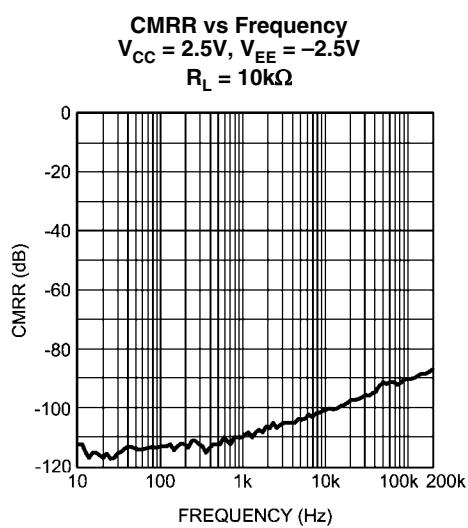
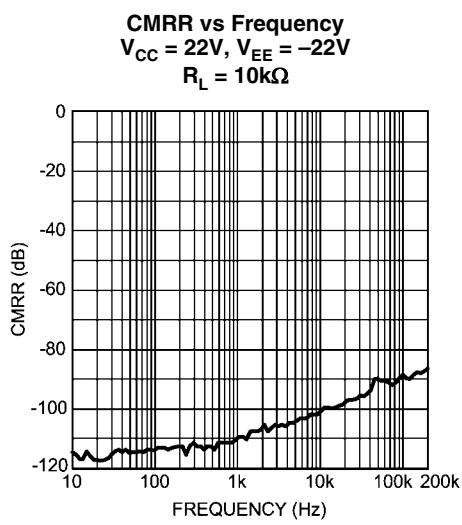
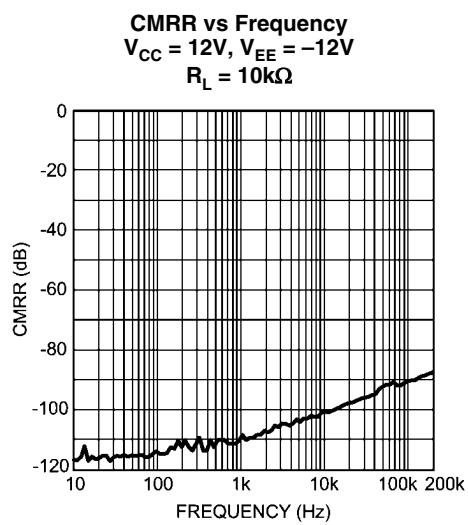
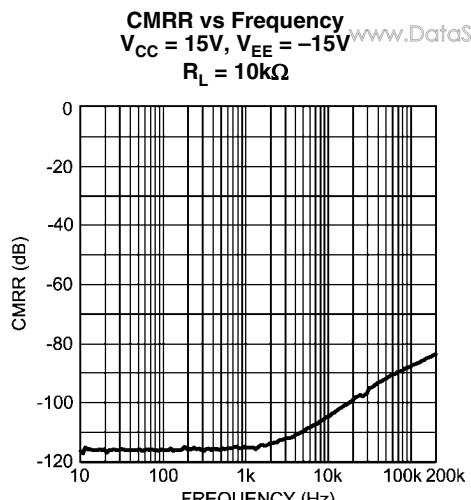
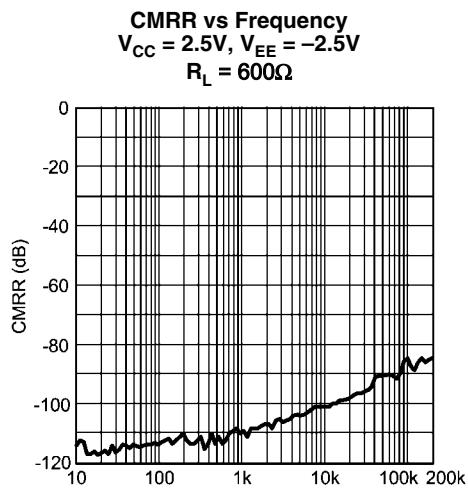
300194r6



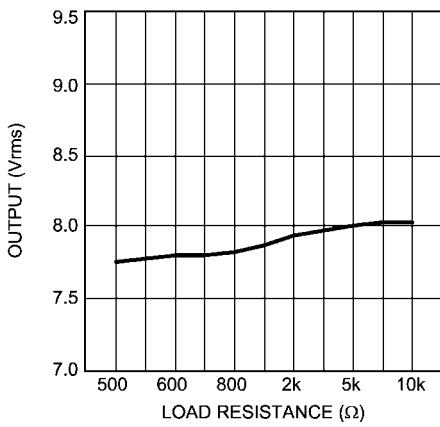
300194p5





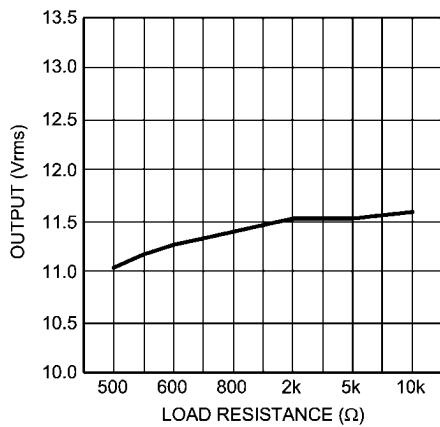


Output Voltage vs Load Resistance
 $V_{CC} = 12V$, $V_{EE} = -12V$
 THD+N = 1%



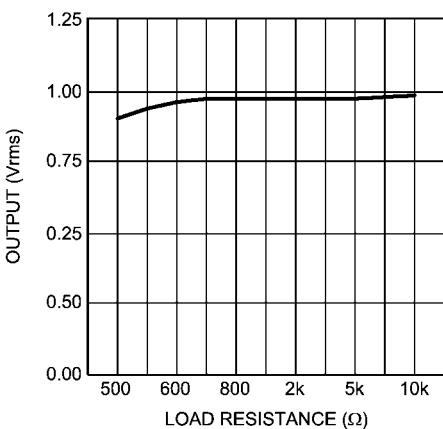
300194h0

Output Voltage vs Load Resistance
 $V_{CC} = 22V$, $V_{EE} = -22V$
 THD+N = 1%



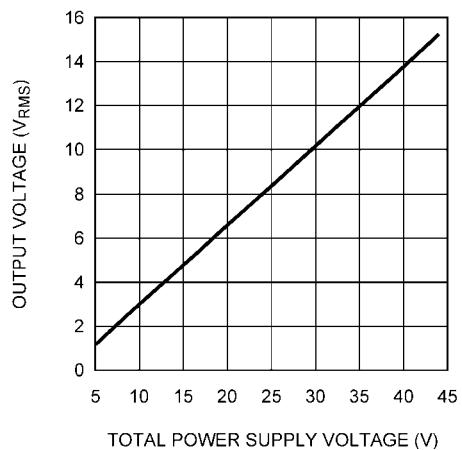
300194h2

Output Voltage vs Load Resistance
 $V_{CC} = 2.5V$, $V_{EE} = -2.5V$
 THD+N = 1%



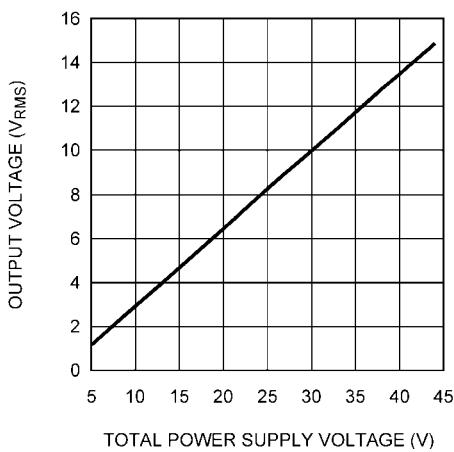
300194g9

Output Voltage vs Total Power Supply Voltage
 $R_L = 2k\Omega$, THD+N = 1%



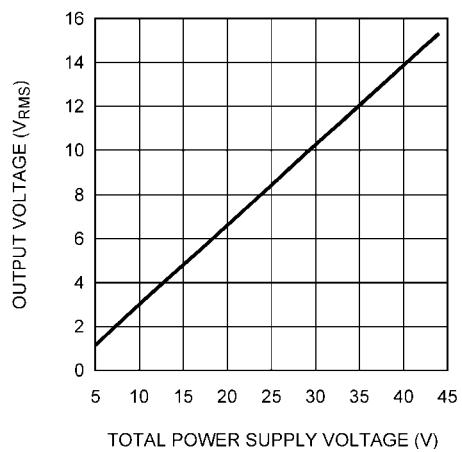
30019407

Output Voltage vs Total Power Supply Voltage
 $R_L = 600\Omega$, THD+N = 1%



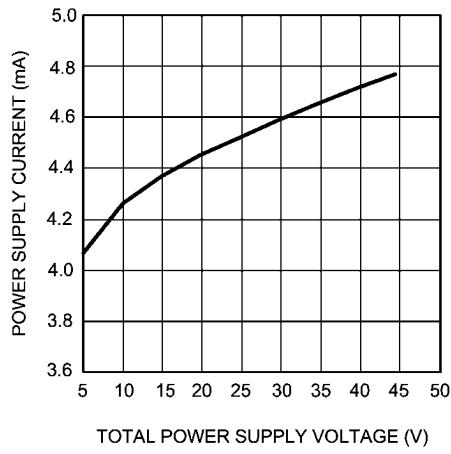
30019409

Output Voltage vs Total Power Supply Voltage
 $R_L = 10k\Omega$, THD+N = 1%



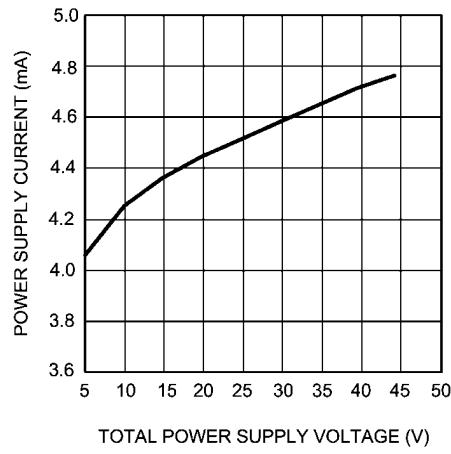
30019408

Power Supply Current vs Total Power Supply Voltage

 $R_L = 2\text{k}\Omega$ 

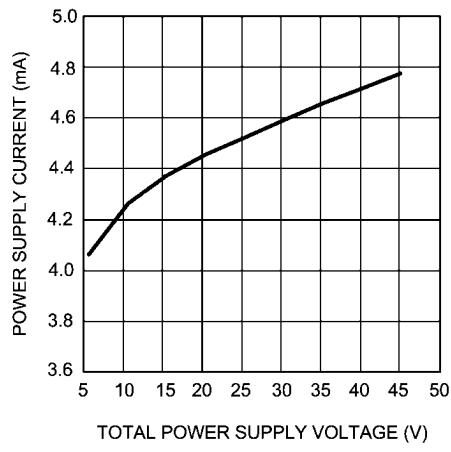
30019413

Power Supply Current vs Total Power Supply Voltage

 $R_L = 600\Omega$ 

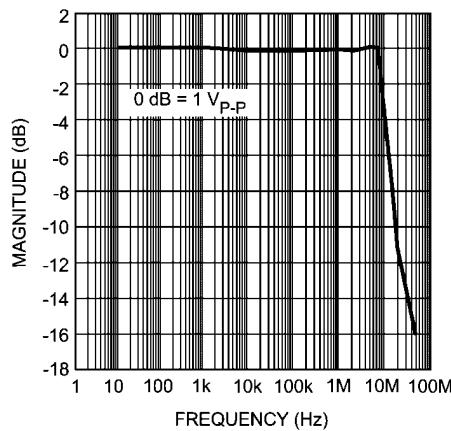
30019415

Power Supply Current vs Total Power Supply Voltage

 $R_L = 10\text{k}\Omega$ 

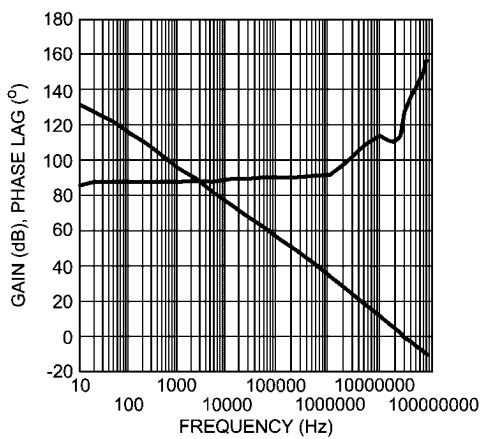
30019414

Full Power Bandwidth vs Frequency

 $V_S = \pm 18\text{V}, R_L = 2\text{k}\Omega$ 

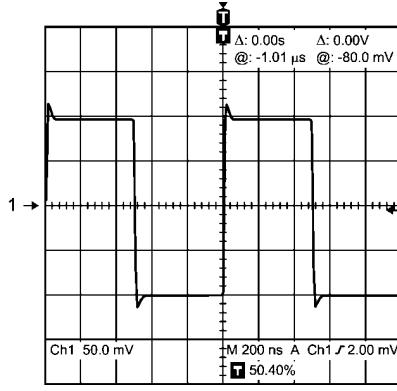
300194j0

Gain Phase vs Frequency

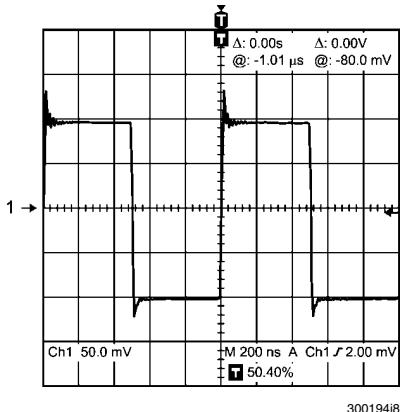
 $V_S = \pm 18\text{V}, R_L = 2\text{k}\Omega$ 

300194j1

Small-Signal Transient Response

 $A_V = 1, C_L = 10\text{pF}$ 

300194j7

Small-Signal Transient Response
 $A_V = 1, C_L = 100\text{pF}$ www.DataSheet4U.com

300194i8

Application Information

DISTORTION MEASUREMENTS

The vanishingly low residual distortion produced by LME49870 is below the capabilities of all commercially available equipment. This makes distortion measurements just slightly more difficult than simply connecting a distortion meter to the amplifier's inputs and outputs. The solution, however, is quite simple: an additional resistor. Adding this resistor extends the resolution of the distortion measurement equipment.

The LME49870's low residual distortion is an input referred internal error. As shown in Figure 1, adding the 10Ω resistor connected between the amplifier's inverting and non-inverting

inputs changes the amplifier's noise gain. The result is that the error signal (distortion) is amplified by a factor of 101.¹ Although the amplifier's closed-loop gain is unaltered, the feedback available to correct distortion errors is reduced by 101, which means that measurement resolution increases by 101. To ensure minimum effects on distortion measurements, keep the value of R1 low as shown in Figure 1.

This technique is verified by duplicating the measurements with high closed loop gain and/or making the measurements at high frequencies. Doing so produces distortion components that are within the measurement equipment's capabilities. This datasheet's THD+N and IMD values were generated using the above described circuit connected to an Audio Precision System Two Cascade.

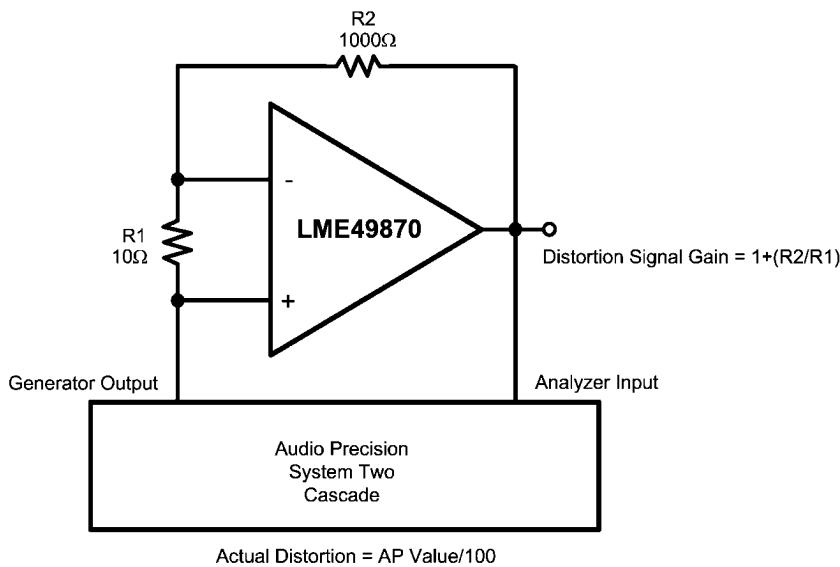
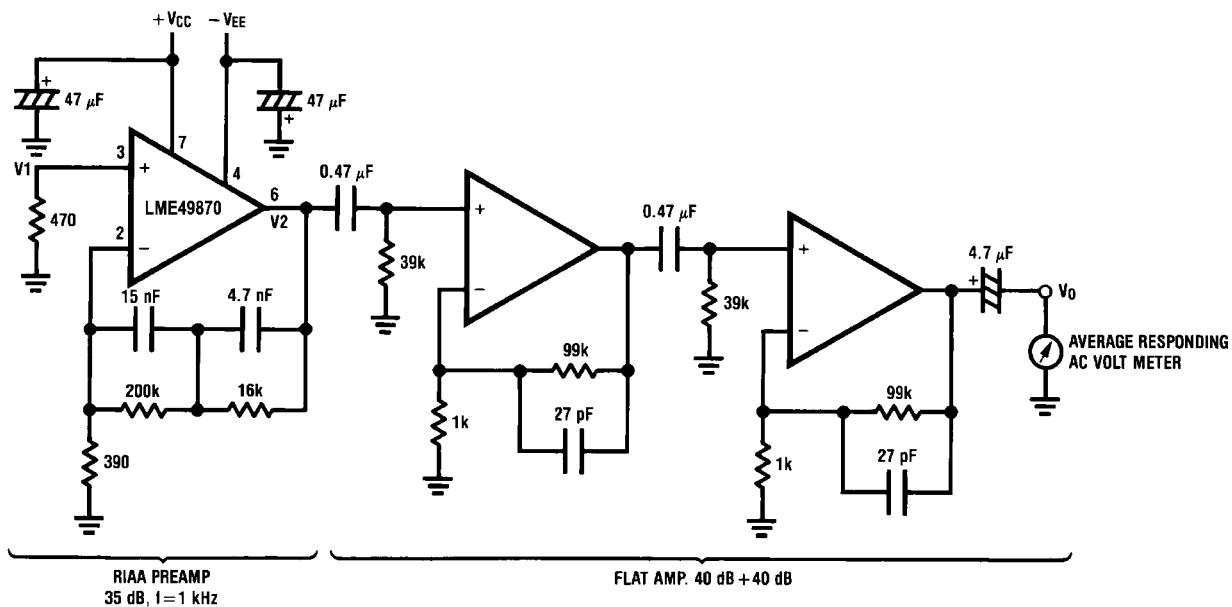


FIGURE 1. THD+N and IMD Distortion Test Circuit

The LME49870 is a high speed op amp with excellent phase margin and stability. Capacitive loads up to 100pF will cause little change in the phase characteristics of the amplifiers and are therefore allowable.

Capacitive loads greater than 100pF must be isolated from the output. The most straightforward way to do this is to put

a resistor in series with the output. This resistor will also prevent excess power dissipation if the output is accidentally shorted.

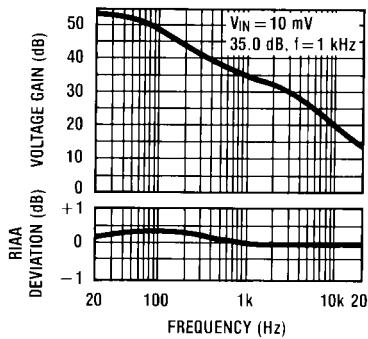


Complete shielding is required to prevent induced pick up from external sources. Always check with oscilloscope for power line noise.

30019427

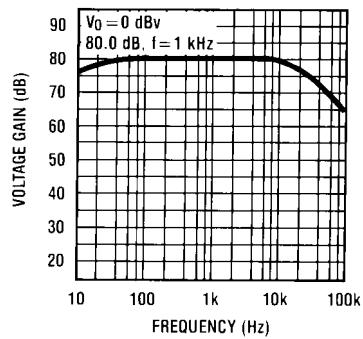
Noise Measurement Circuit
Total Gain: 115 dB @ $f = 1 \text{ kHz}$
Input Referred Noise Voltage: $e_n = V_0/560,000 \text{ (V)}$

RIAA Preamplifier Voltage Gain, RIAA Deviation vs Frequency



30019428

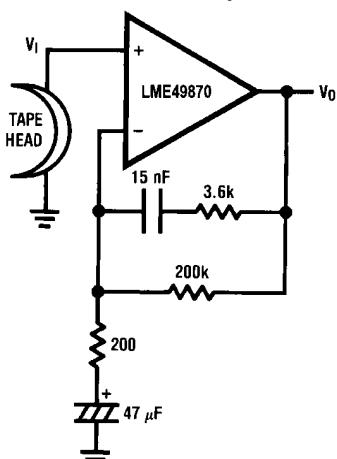
Flat Amp Voltage Gain vs Frequency



30019429

TYPICAL APPLICATIONS

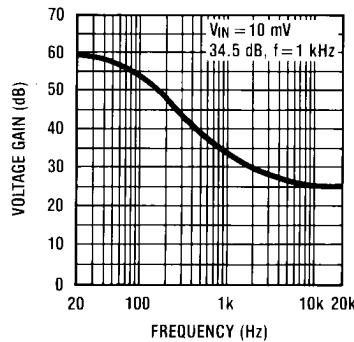
NAB Preamp



30019430

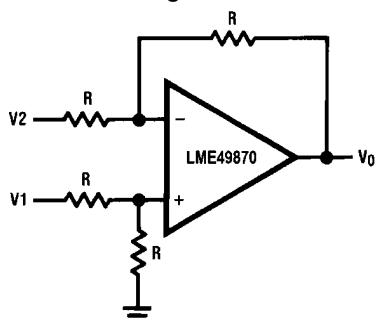
$A_V = 34.5$
 $F = 1 \text{ kHz}$
 $E_n = 0.38 \mu\text{V}$
A Weighted

NAB Preamp Voltage Gain vs Frequency



30019431

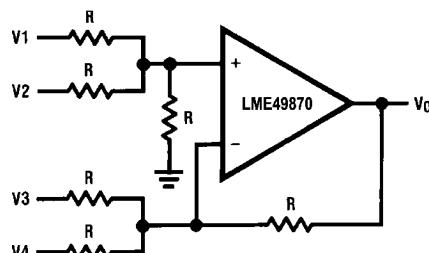
Balanced to Single Ended Converter



30019432

 $V_O = V1 - V2$

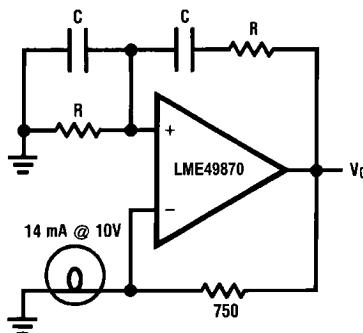
Adder/Subtractor



30019433

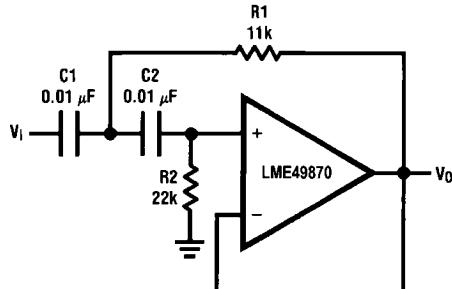
$$V_O = V1 + V2 - V3 - V4$$

Sine Wave Oscillator

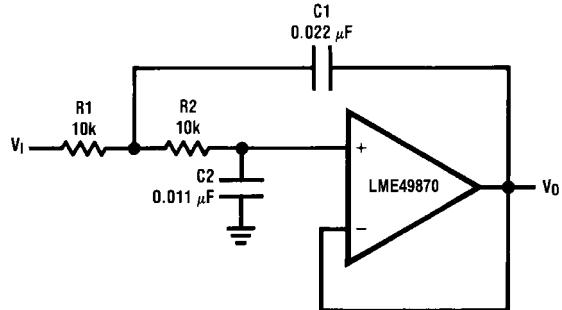


30019434

$$f_0 = \frac{1}{2\pi RC}$$

**Second Order High Pass Filter
(Butterworth)**


30019435

**Second Order Low Pass Filter
(Butterworth)**


30019436

if $C_1 = C_2 = C$

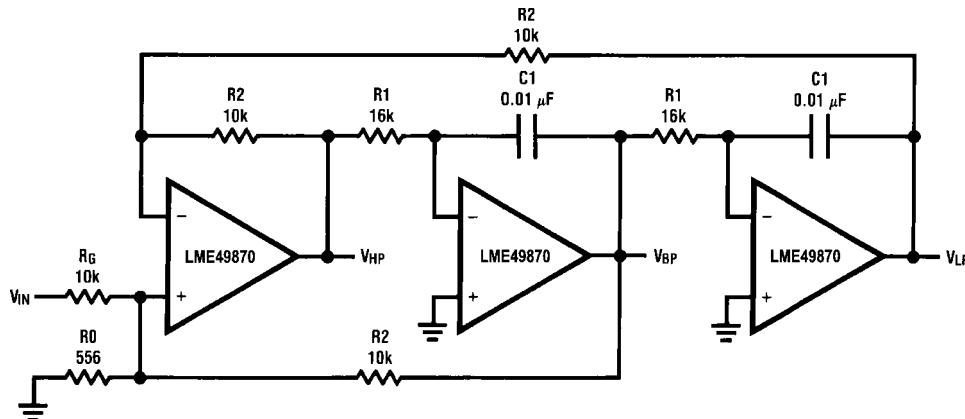
$$R_1 = \frac{\sqrt{2}}{2\omega_0 C}$$

$$R_2 = 2 \cdot R_1$$

Illustration is $f_0 = 1$ kHzif $R_1 = R_2 = R$

$$C_1 = \frac{\sqrt{2}}{\omega_0 R}$$

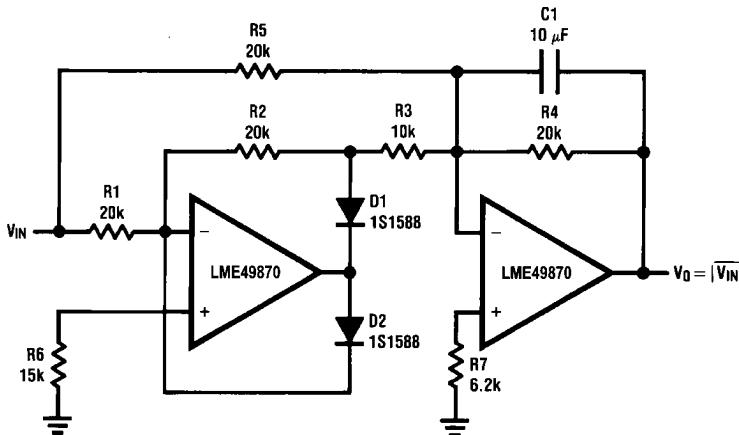
$$C_2 = \frac{C_1}{2}$$

Illustration is $f_0 = 1$ kHz
State Variable Filter


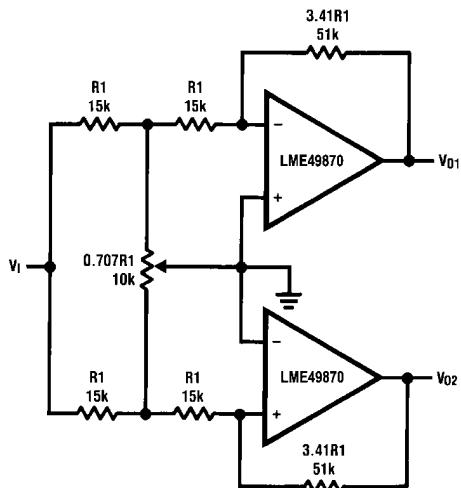
30019437

$$f_0 = \frac{1}{2\pi C_1 R_1}, Q = \frac{1}{2} \left(1 + \frac{R_2}{R_0} + \frac{R_2}{R_G} \right), A_{BP} = Q A_{LP} = Q A_{LH} = \frac{R_2}{R_G}$$

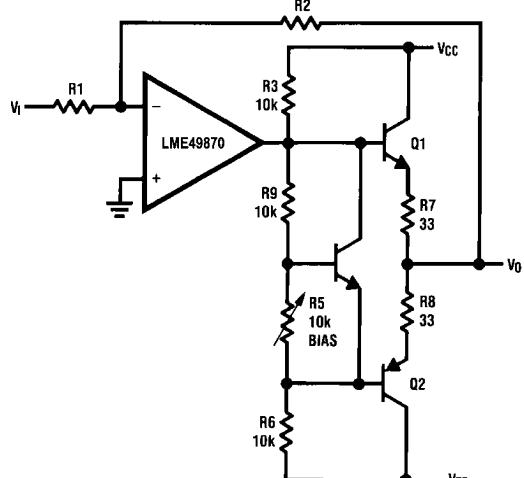
Illustration is $f_0 = 1$ kHz, $Q = 10$, $A_{BP} = 1$

AC/DC Converter

30019438

2 Channel Panning Circuit (Pan Pot)

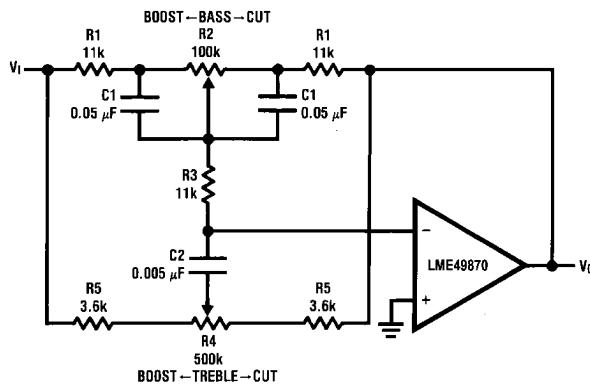
30019439

Line Driver

30019440

Tone Control

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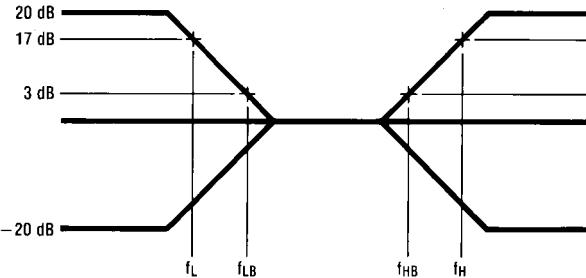


30019441

$$f_L = \frac{1}{2\pi R_2 C_1}, f_{LB} = \frac{1}{2\pi R_1 C_1}$$

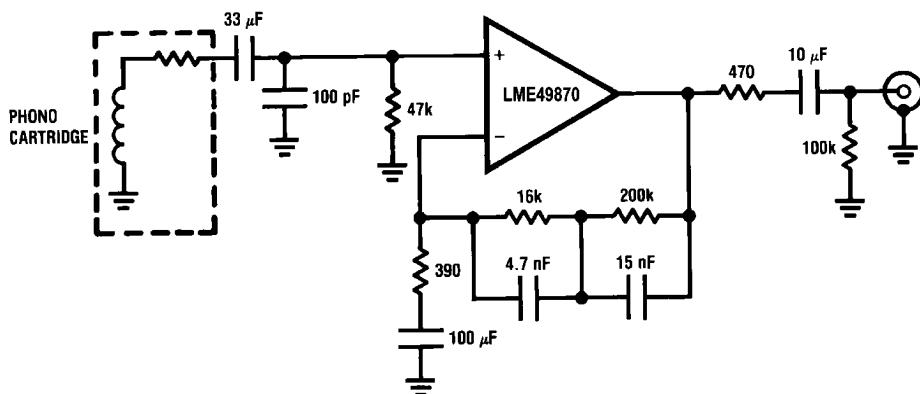
$$f_H = \frac{1}{2\pi R_5 C_2}, f_{HB} = \frac{1}{2\pi(R_1 + R_5 + 2R_3)C_2}$$

Illustration is:

 $f_L = 32$ Hz, $f_{LB} = 320$ Hz $f_H = 11$ kHz, $f_{HB} = 1.1$ kHz

30019442

RIAA Preamp



30019403

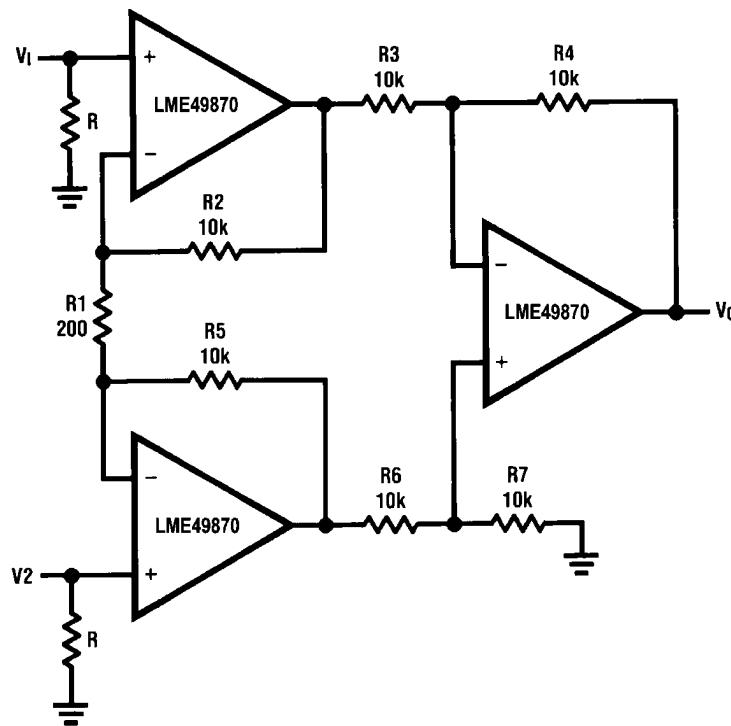
 $A_v = 35$ dB $E_n = 0.33$ μ V

S/N = 90 dB

 $f = 1$ kHz

A Weighted

A Weighted, $V_{IN} = 10$ mV@ $f = 1$ kHz

Balanced Input Mic Amp

30019443

If R₂ = R₅, R₃ = R₆, R₄ = R₇

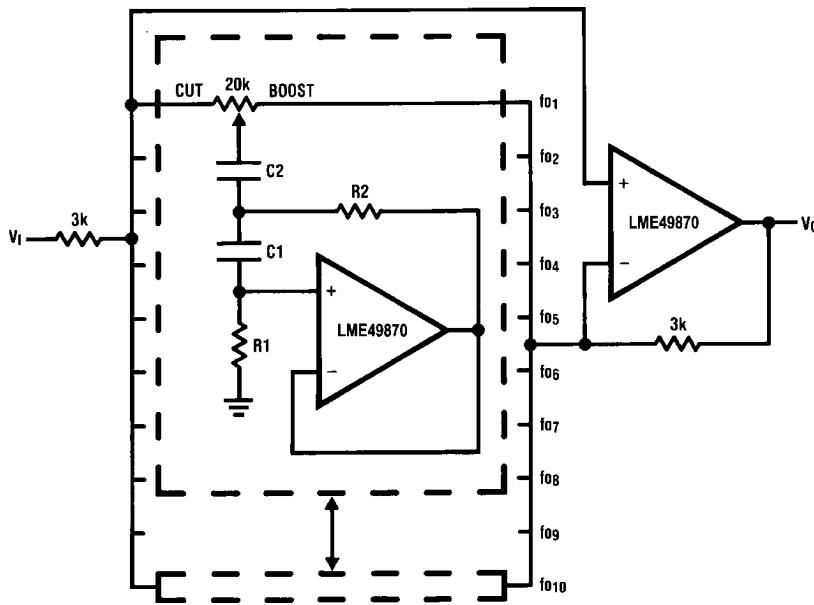
$$V_0 = \left(1 + \frac{2R_2}{R_1}\right) \frac{R_4}{R_3} (V_2 - V_1)$$

Illustration is:

$$V_0 = 101(V_2 - V_1)$$

10 Band Graphic Equalizer

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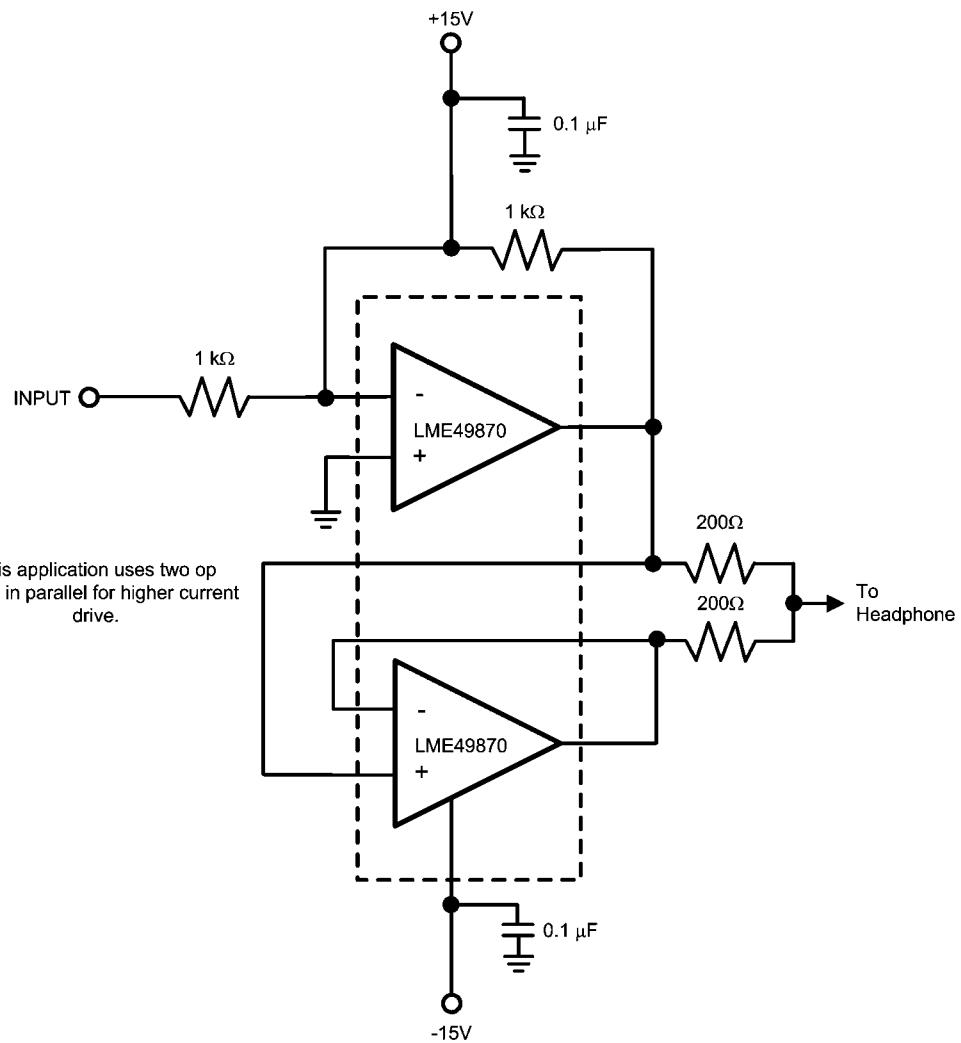
30019444

f_0 (Hz)	C_1	C_2	R_1	R_2
32	0.12 μ F	4.7 μ F	75k Ω	500 Ω
64	0.056 μ F	3.3 μ F	68k Ω	510 Ω
125	0.033 μ F	1.5 μ F	62k Ω	510 Ω
250	0.015 μ F	0.82 μ F	68k Ω	470 Ω
500	8200pF	0.39 μ F	62k Ω	470 Ω
1k	3900pF	0.22 μ F	68k Ω	470 Ω
2k	2000pF	0.1 μ F	68k Ω	470 Ω
4k	1100pF	0.056 μ F	62k Ω	470 Ω
8k	510pF	0.022 μ F	68k Ω	510 Ω
16k	330pF	0.012 μ F	51k Ω	510 Ω

Note 9: At volume of change = ± 12 dB

Q = 1.7

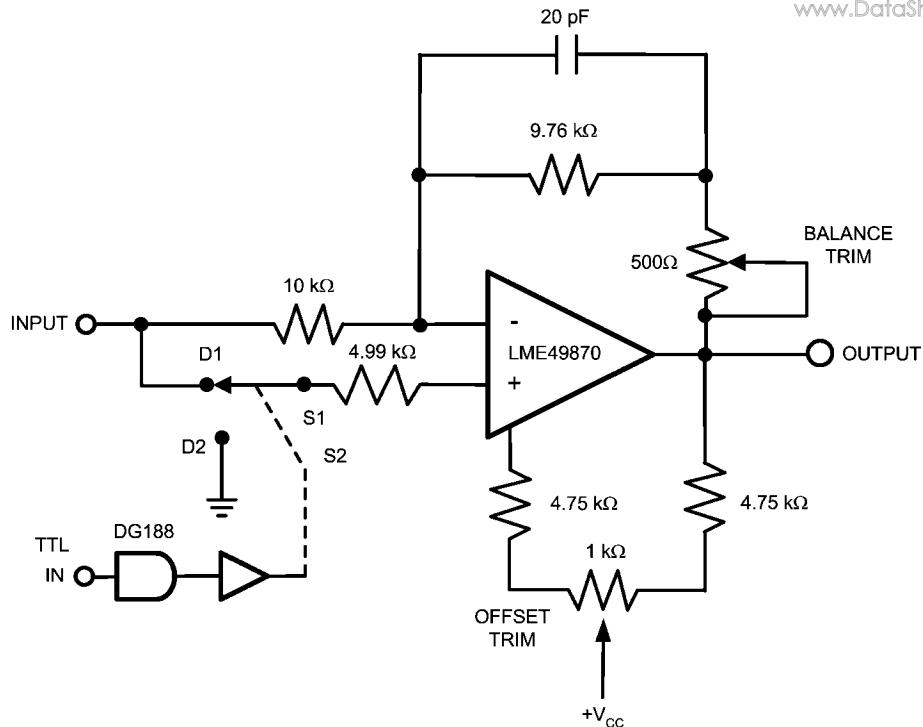
Reference: "AUDIO/RADIO HANDBOOK", National Semiconductor, 1980, Page 2-61

Headphone Amplifier

30019410

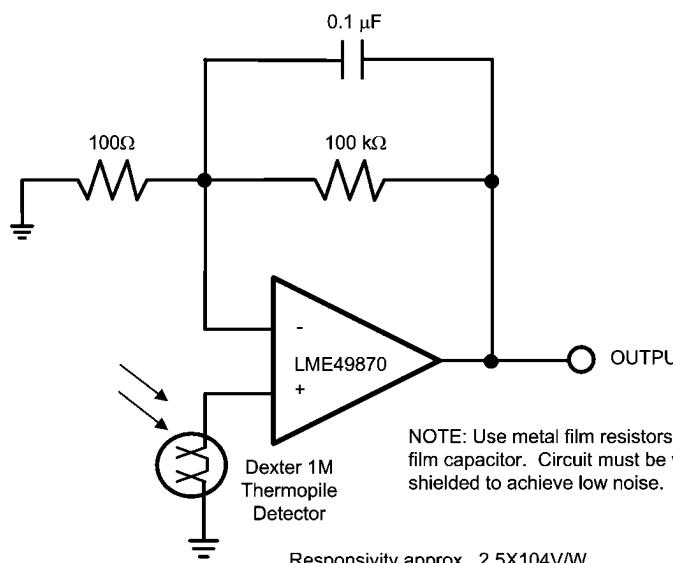
High Performance Synchronous Demodulator

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30019411

Long-Wavelength Infrared Detector Amplifier



30019412

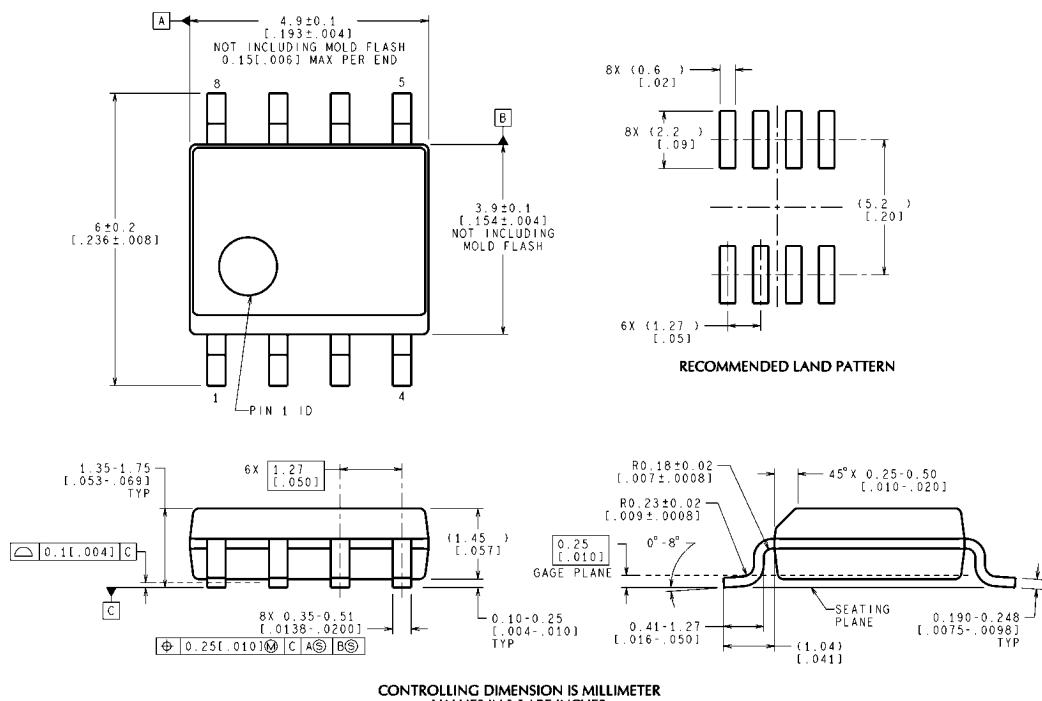
Revision History

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Rev	Date	Description
1.0	09/20/07	Initial release.
1.1	09/27/07	Updated Notes 1–7 (per National standard).
1.2	12/20/07	Deleted all Crosstalk vs Frequency curves.
1.3	01/14/08	Edited some graphics.

Physical Dimensions

inches (millimeters) unless otherwise noted

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Narrow SOIC Package
Order Number LME49870MA
NS Package Number M08A

M08A (Rev L)

Notes

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LME49870

Notes

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